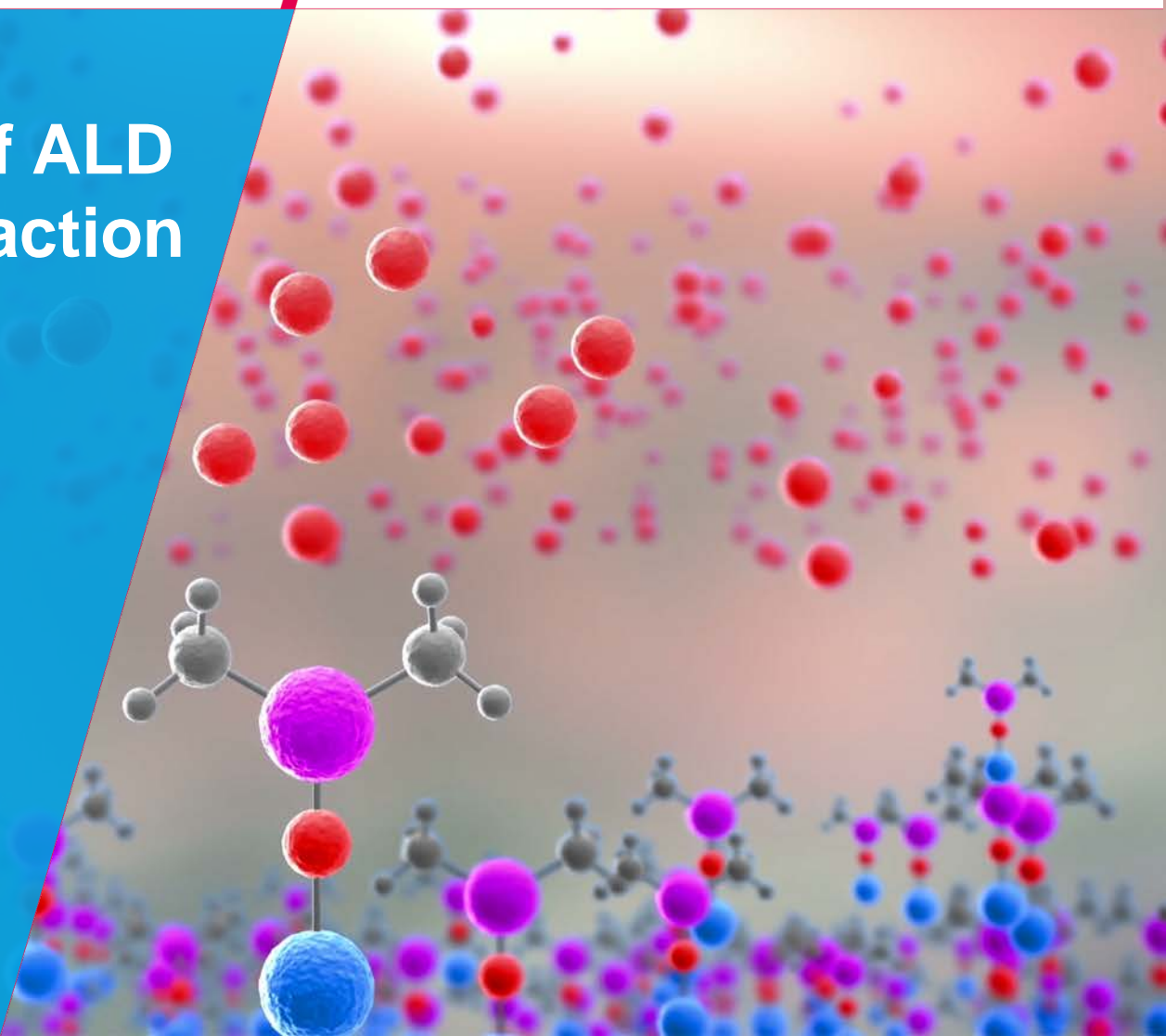


In situ Studies of ALD Processes & Reaction Mechanisms

Erwin Kessels

w.m.m.kessels@tue.nl

www.tue.nl/pmp



This tutorial presentation will give ...

- (1) an overview of **methods** for *in situ* studies of ALD processes & reaction mechanisms; and
- (2) some **insight** into these processes and mechanisms

Don't expect:

- A comprehensive overview
- Techniques explained in large detail

Do expect:

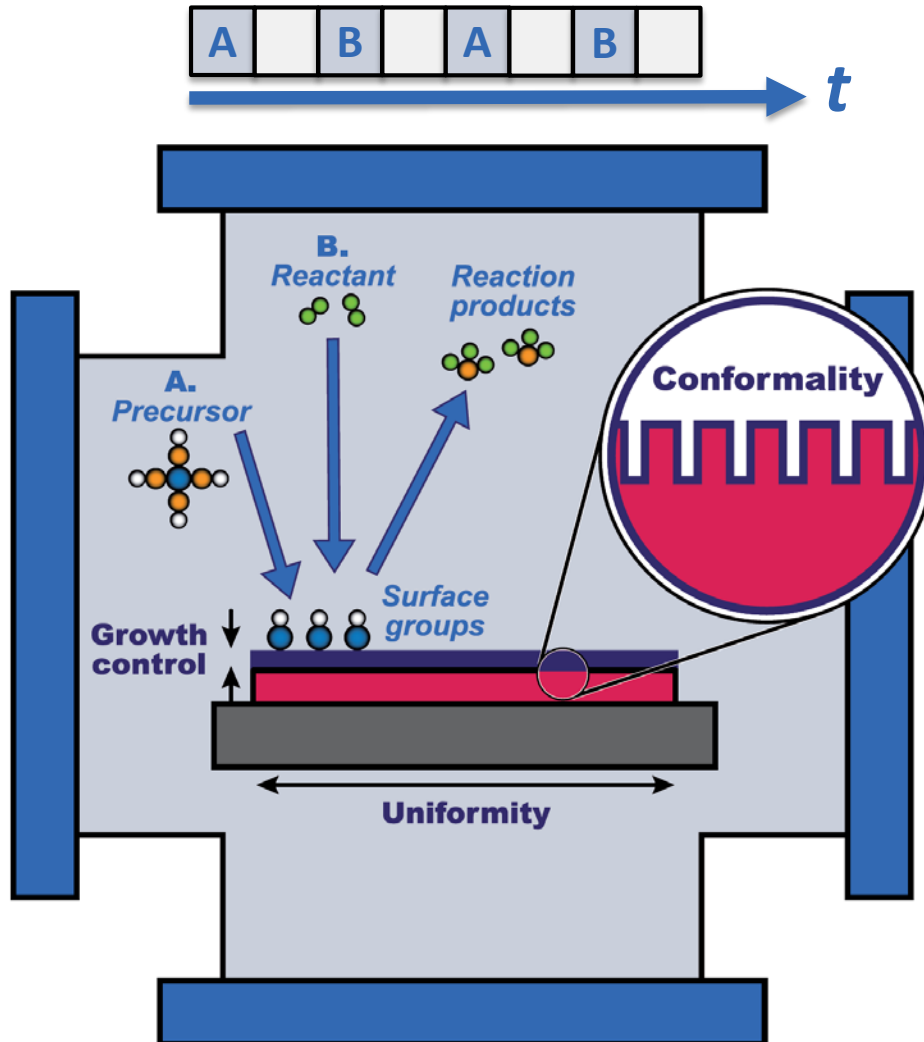
- Focus on what can be learned from the methods
- Their pros and cons articulated & practical comments
- An overview based mainly from own experience



For more information & feedback
see blog:

www.AtomicLimits.com

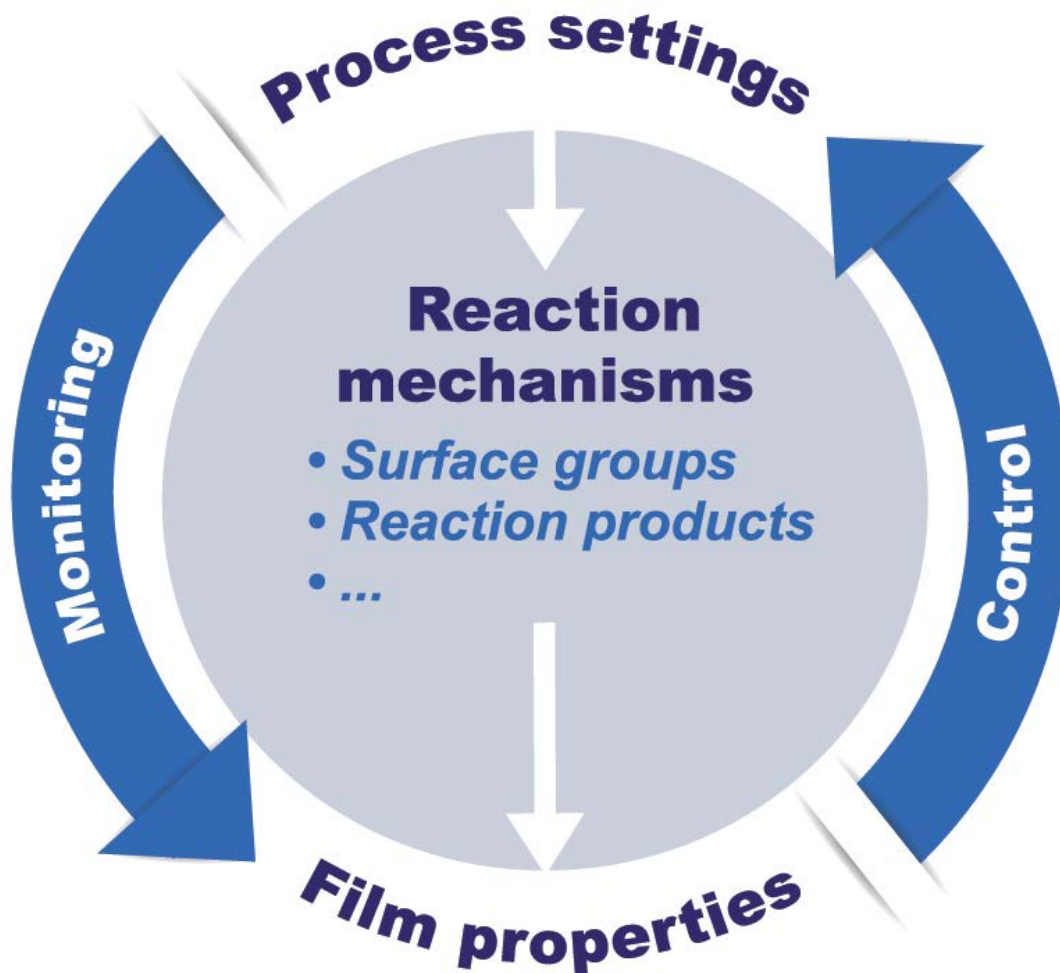
Atomic layer deposition (ALD)



In situ studies:

- Quartz crystal microbalance
- Spectroscopic ellipsometry
- Mass spectrometry
- Gas phase infrared spect.
- Surface infrared spect.
- Optical emission spect.
- X-ray photoelectron spect.
- X-ray diffraction
- Sum-frequency generation
- Adsorption calorimetry
- Scanning tunneling micros.
- ...

In situ studies of ALD processes



Discussed **today**:

- Quartz crystal microbalance
- Spectroscopic ellipsometry
- Mass spectrometry
- Gas phase infrared spect.
- Surface infrared spect.
- Optical emission spect.
- X-ray photoelectron spect.
- X-ray diffraction
- **Sum-frequency generation**
- **Adsorption calorimetry**
- Scanning tunneling micros.
- ...

In situ studies of ALD processes

ADEQUACY



FEASIBILITY



COMPLEXITY



COSTS

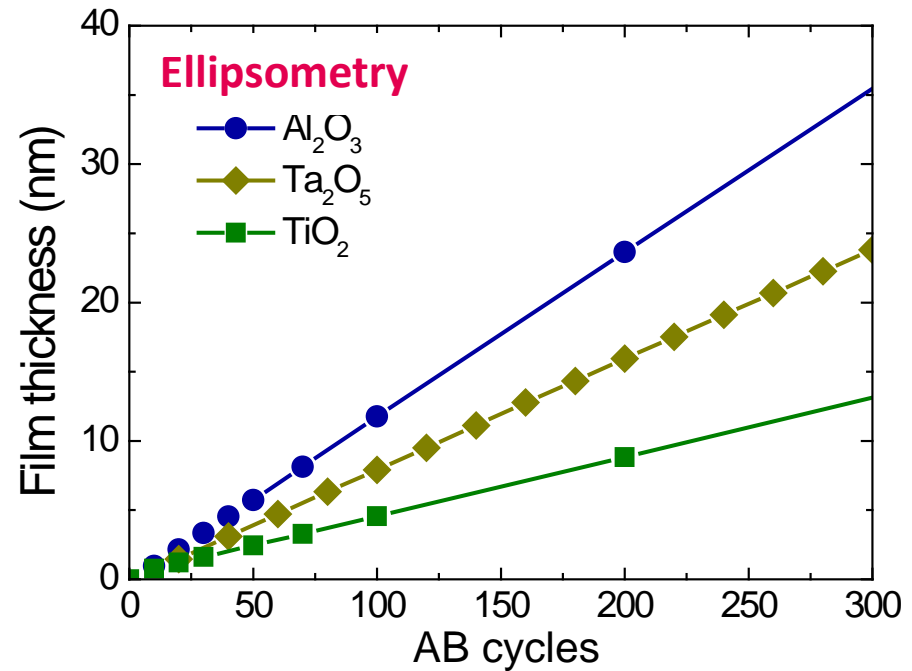
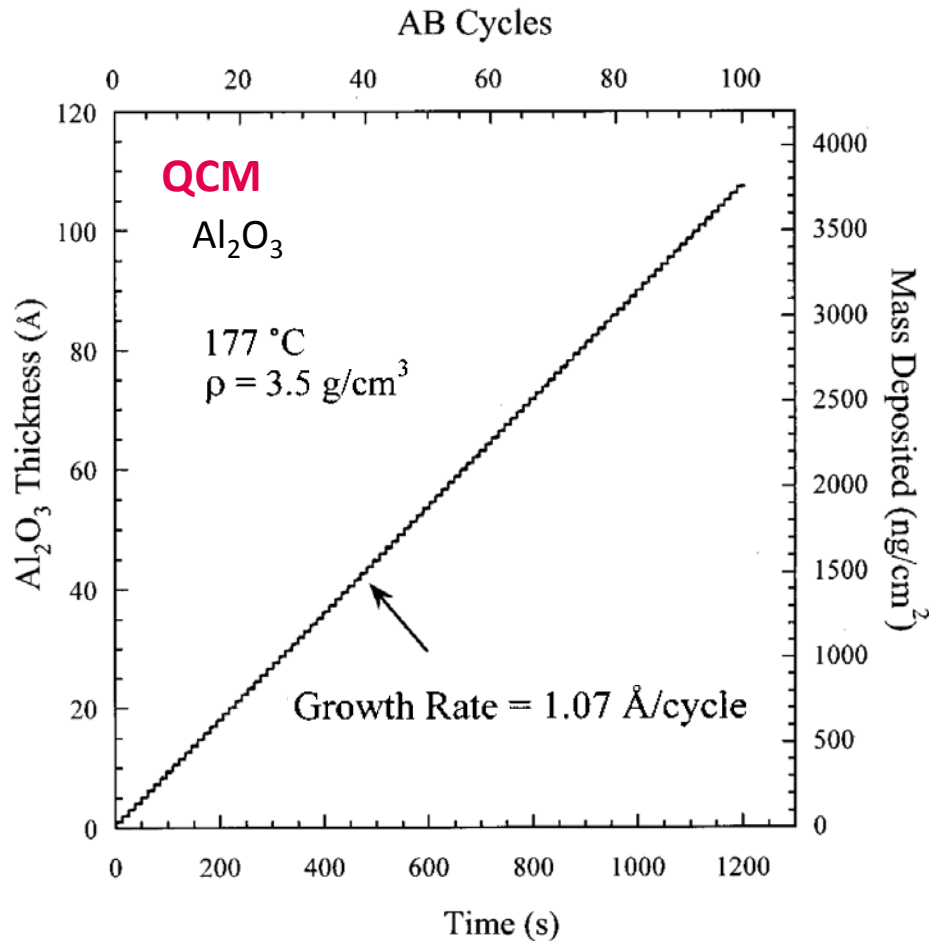


Discussed **today**:

- Quartz crystal microbalance
- Spectroscopic ellipsometry
- Mass spectrometry
- Gas phase infrared spect.
- Surface infrared spect.
- Optical emission spect.

- X-ray photoelectron spect.
- X-ray diffraction
- Sum-frequency generation
- Adsorption calorimetry
- Scanning tunneling micros.
- ...

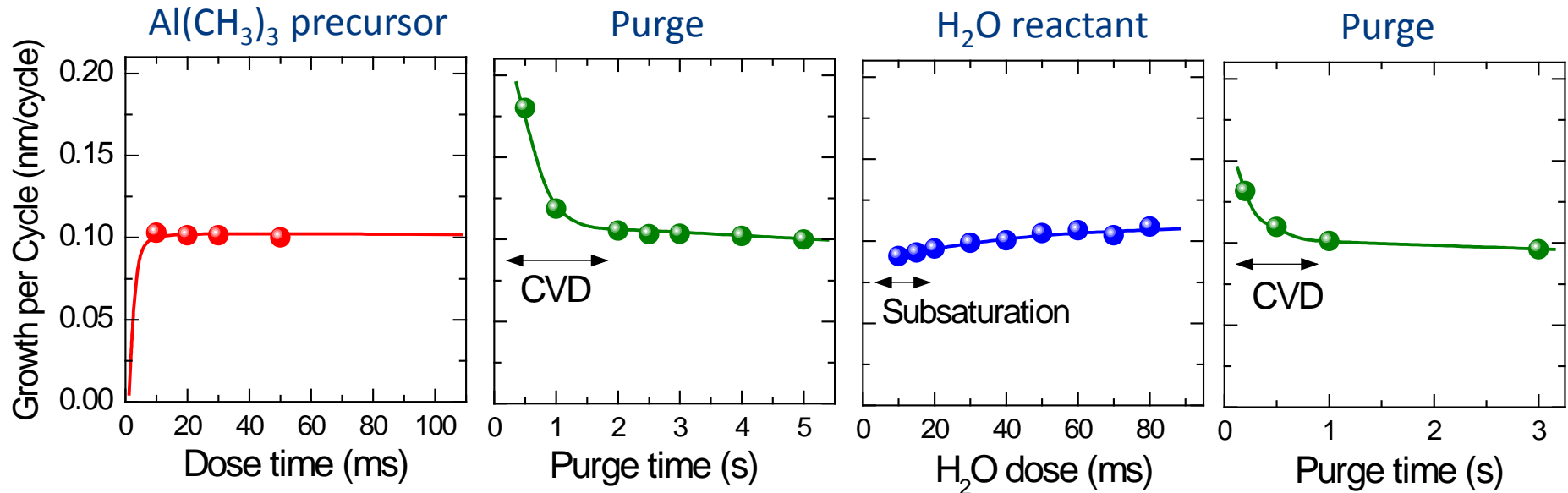
Monitoring (linear) film growth



Material	Growth per cycle
Al_2O_3	1.2 Å (100 °C)
Ta_2O_5	0.80 Å (225 °C)
TiO_2	0.45 Å (200 °C)

ALD saturation curves

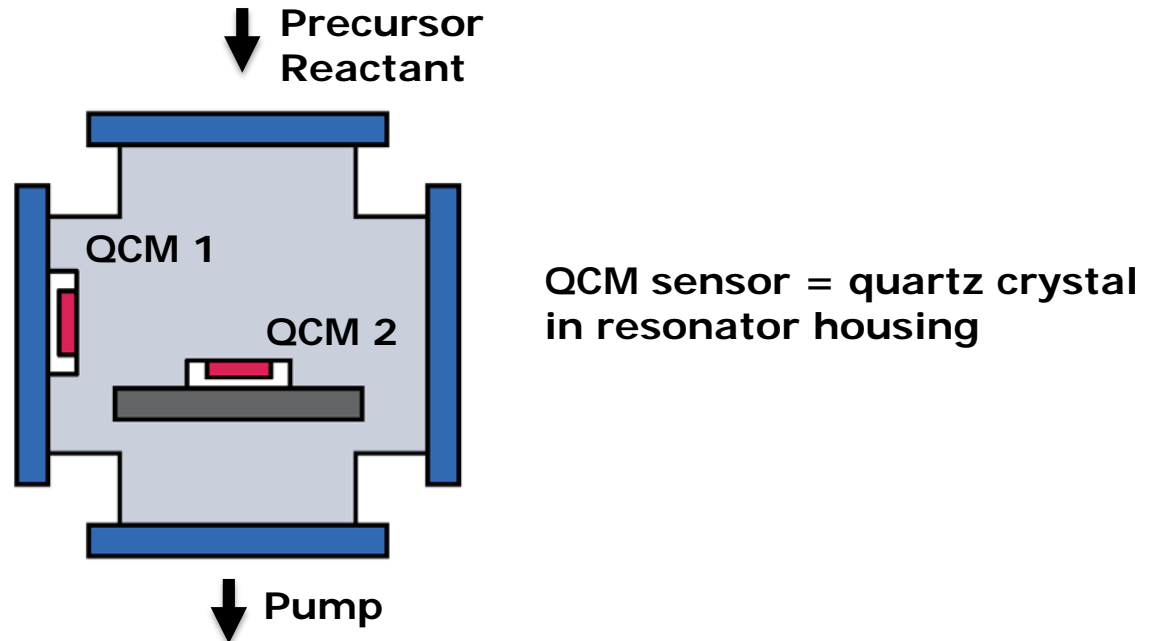
ALD of Al_2O_3 from $\text{Al}(\text{CH}_3)_3$ and H_2O (200 °C)



Vary one parameter while keeping other constant:

$\text{Al}(\text{CH}_3)_3$ – purge – H_2O – purge
20 ms – 2 s – 40 ms – 1 s

Quartz crystal microbalance (QCM)



Measures mass variation of a quartz crystal resonator from its frequency change

- ▲ • Cheap device and relatively easy-to-implement on many reactors
- ▲ • Directly measures mass gain/loss in quantitative way
- ▲ • Very helpful for process development
- ▼ • Very sensitive to variations in pressure, gas flows and temperature

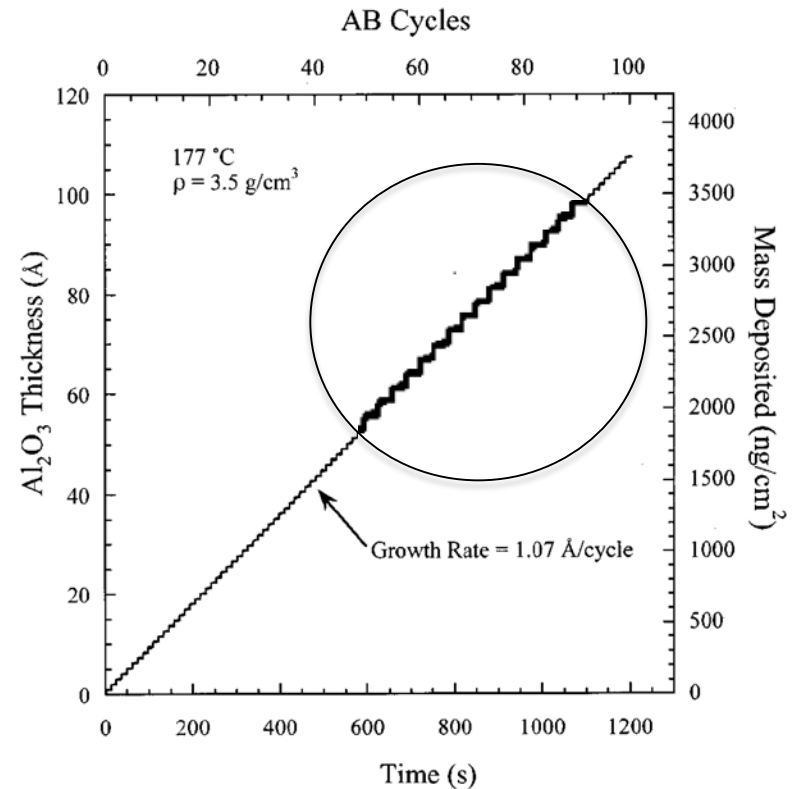
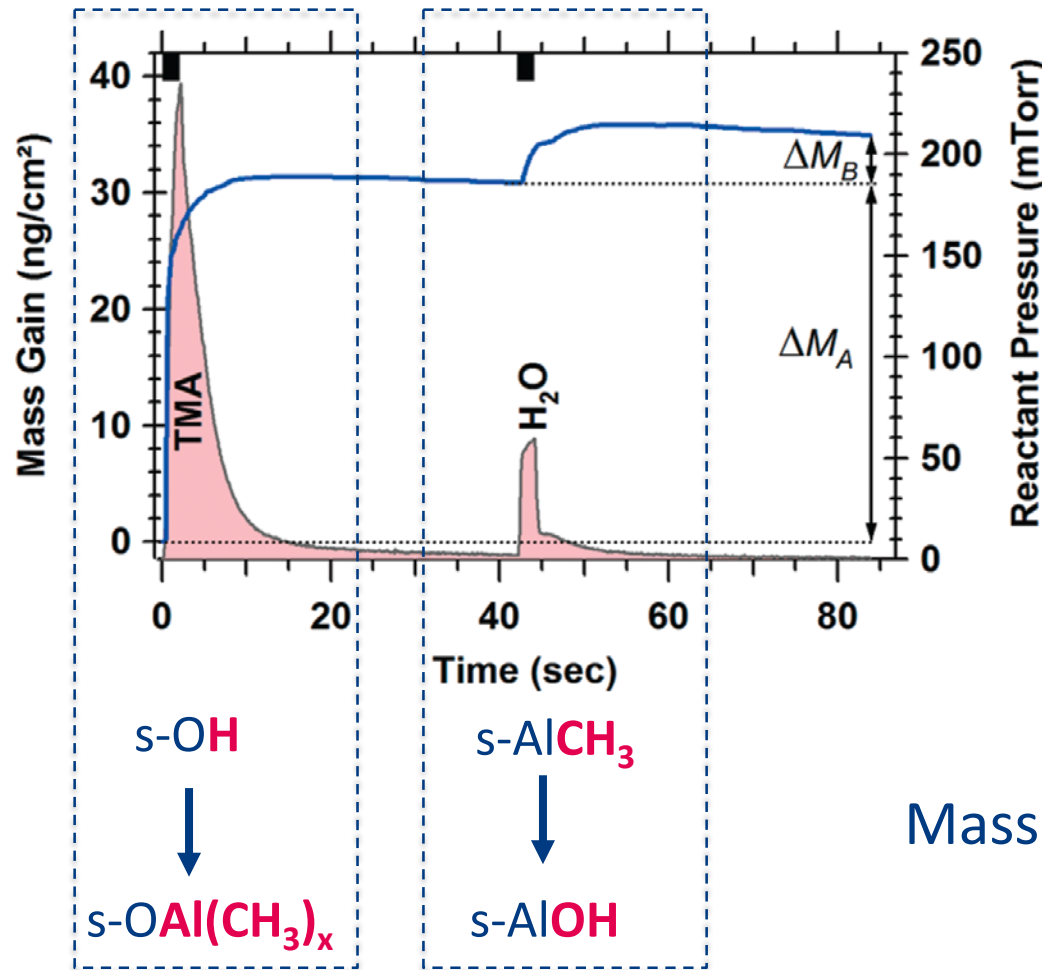
Quartz crystal microbalance (QCM)



Measures mass variation of a quartz crystal resonator from its frequency change

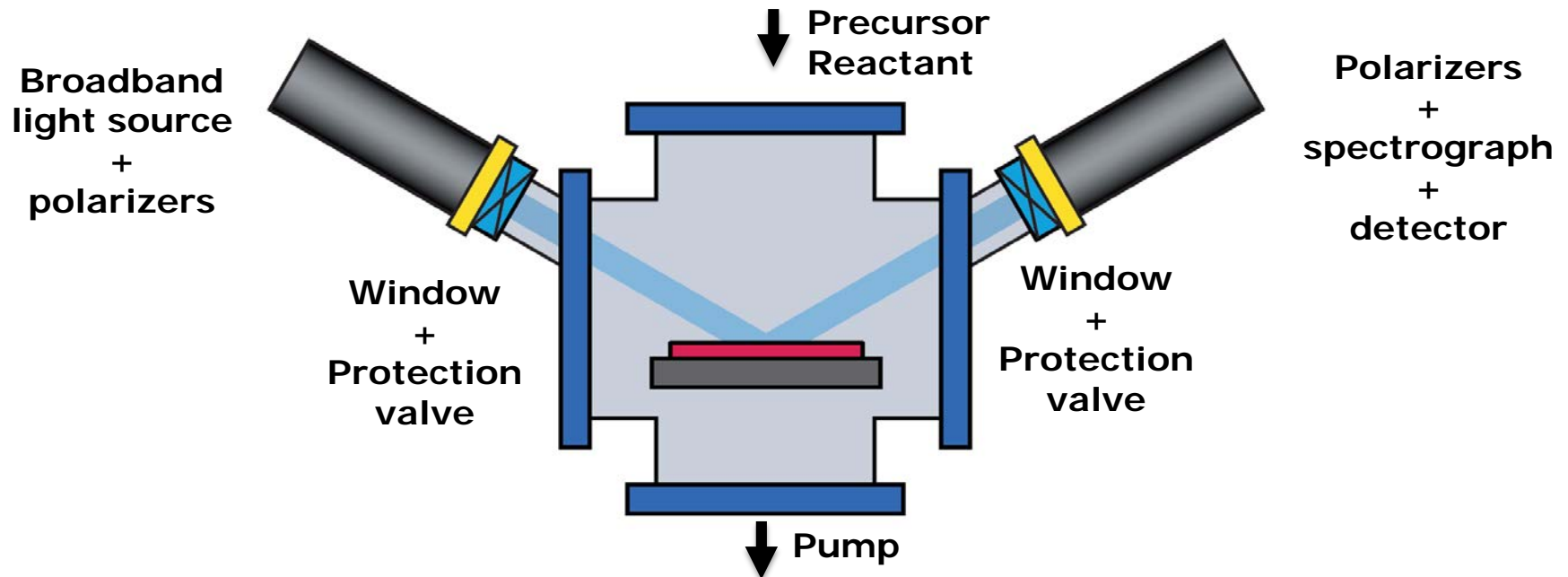
- ▲ • Cheap device and relatively easy-to-implement on many reactors
- ▲ • Directly measures mass gain/loss in quantitative way
- ▲ • Very helpful for process development
- ▼ • Very sensitive to variations in pressure, gas flows and temperature

QCM – Monitoring mass gain (Al_2O_3)



Mass gain/loss can be monitored
per half-cycle

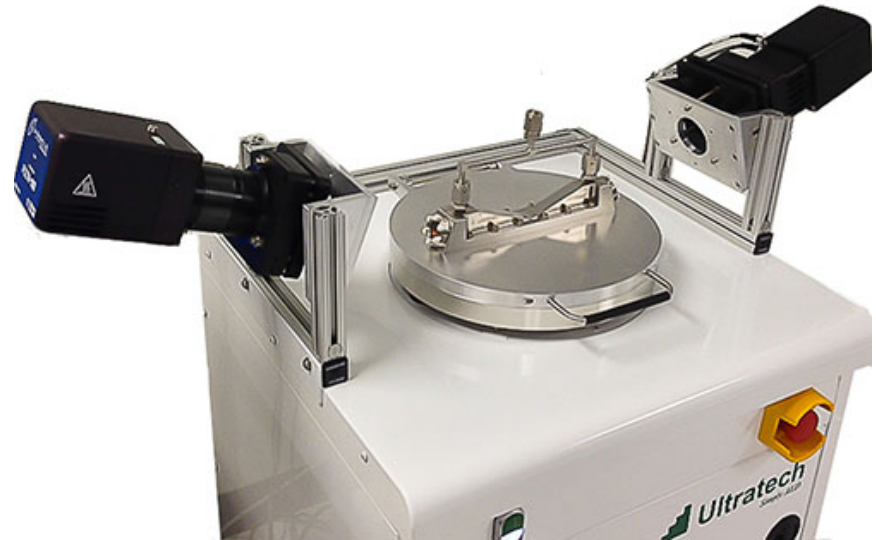
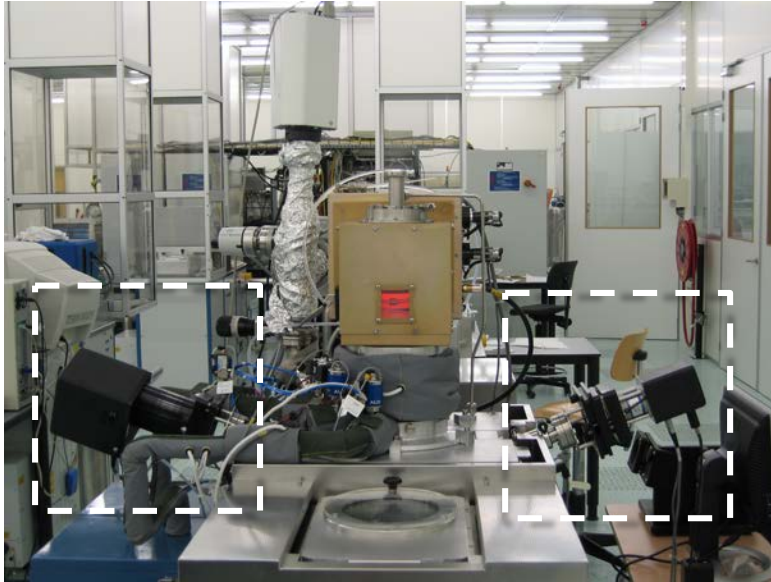
Spectroscopic ellipsometry (SE)



Measures change of polarization of light upon reflection (multiple wavelengths)

- ▲ . Directly measures thickness, very helpful for (fast) process development
- ▲ . Yields also insight into many other material properties (optical/electrical)
- ▼ . Optical modelling can be challenging for some layers/materials
- ▼ . Rather expensive and requires special ports for optical access

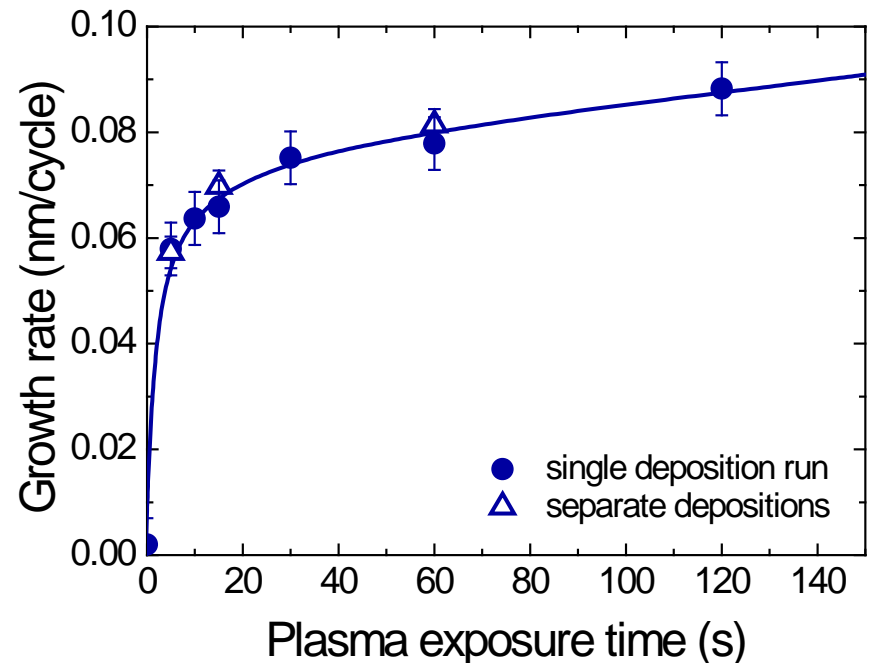
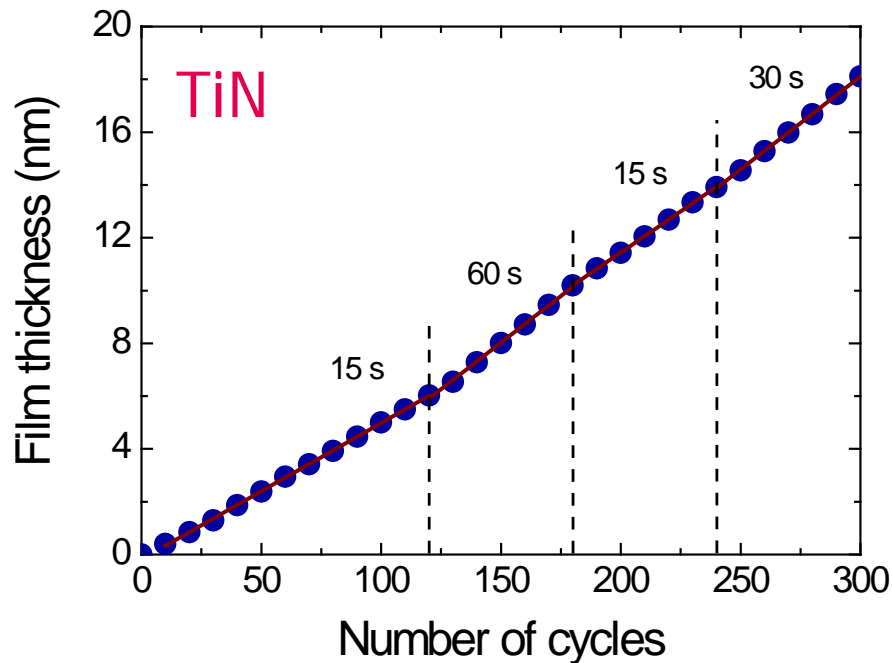
Spectroscopic ellipsometry (SE)



Measures change of polarization of light upon reflection (multiple wavelengths)

- ▲ . Directly measures thickness, very helpful for (fast) process development
- ▲ . Yields also insight into many other material properties (optical/electrical)
- ▼ . Optical modelling can be challenging for some layers/materials
- ▼ . Rather expensive and requires special ports for optical access

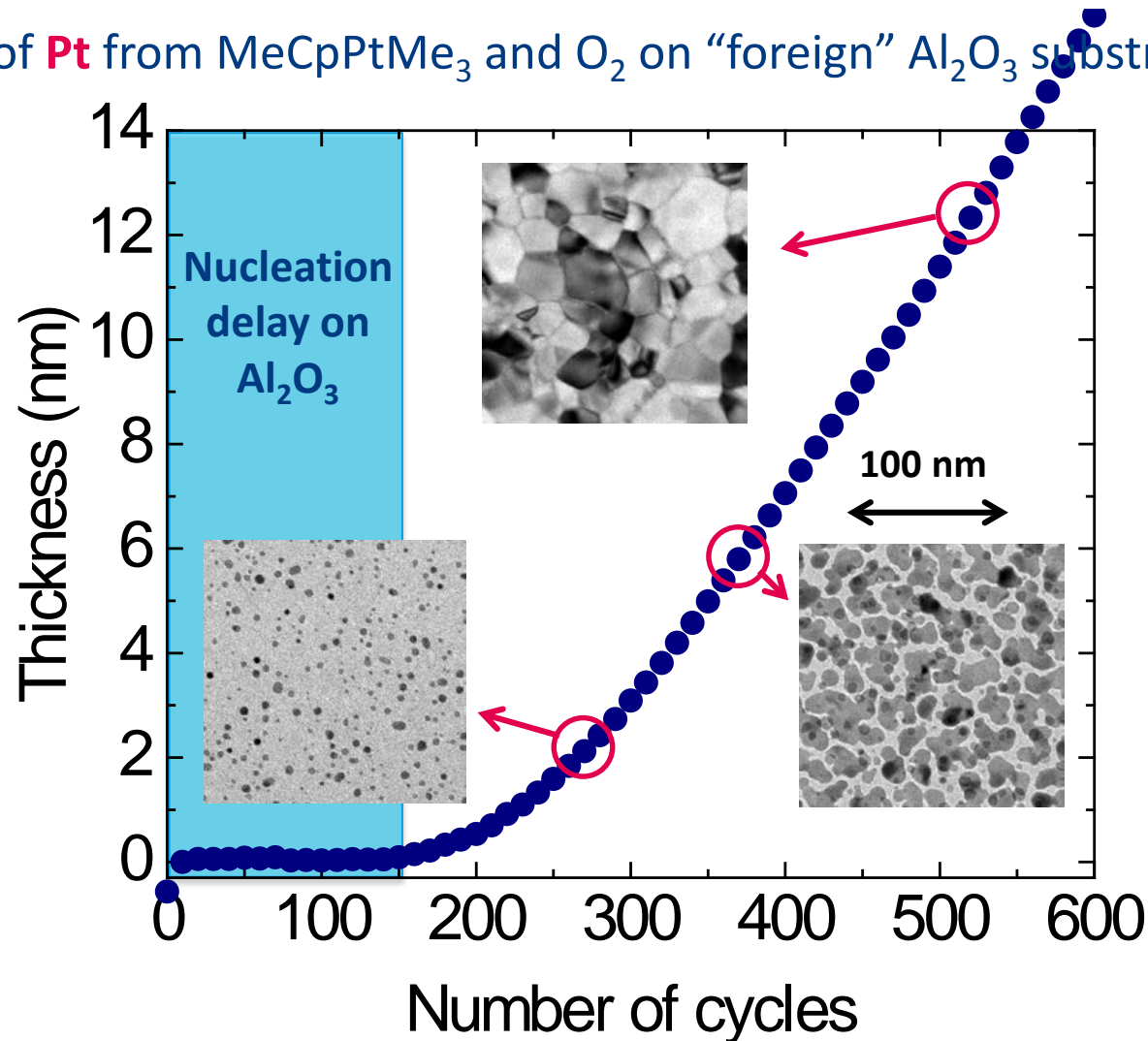
Spectroscopic ellipsometry – Saturation (TiN)



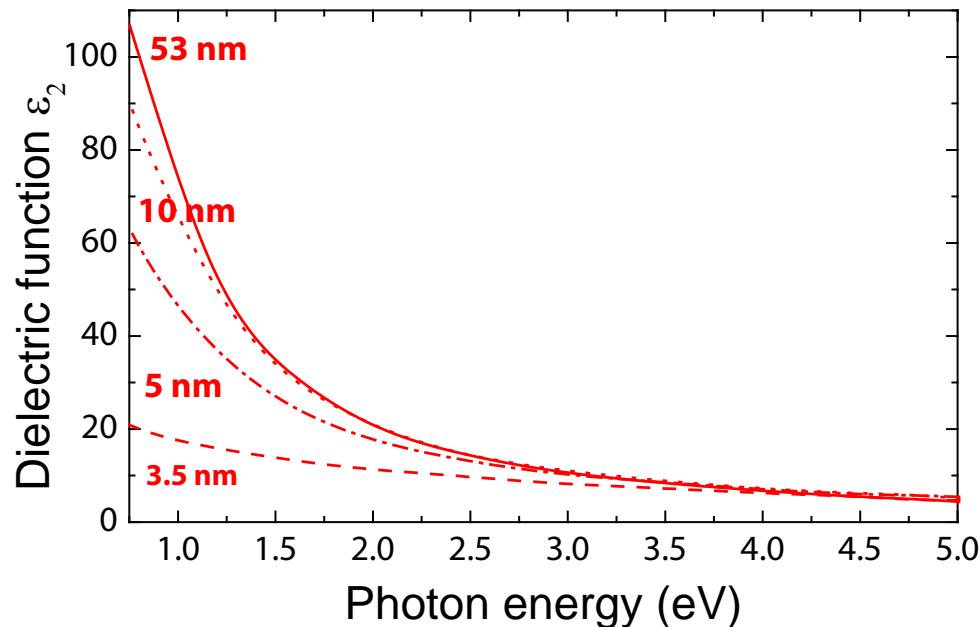
Monitor film thickness while changing precursor/reactant dosing time
provides a **fast method to determine saturation curves**

Spectroscopic ellipsometry – Nucleation (Pt)

ALD of **Pt** from MeCpPtMe_3 and O_2 on “foreign” Al_2O_3 substrate (300°C)



Spectroscopic ellipsometry – Resistivity (Pt)



Imaginary part of dielectric function ϵ

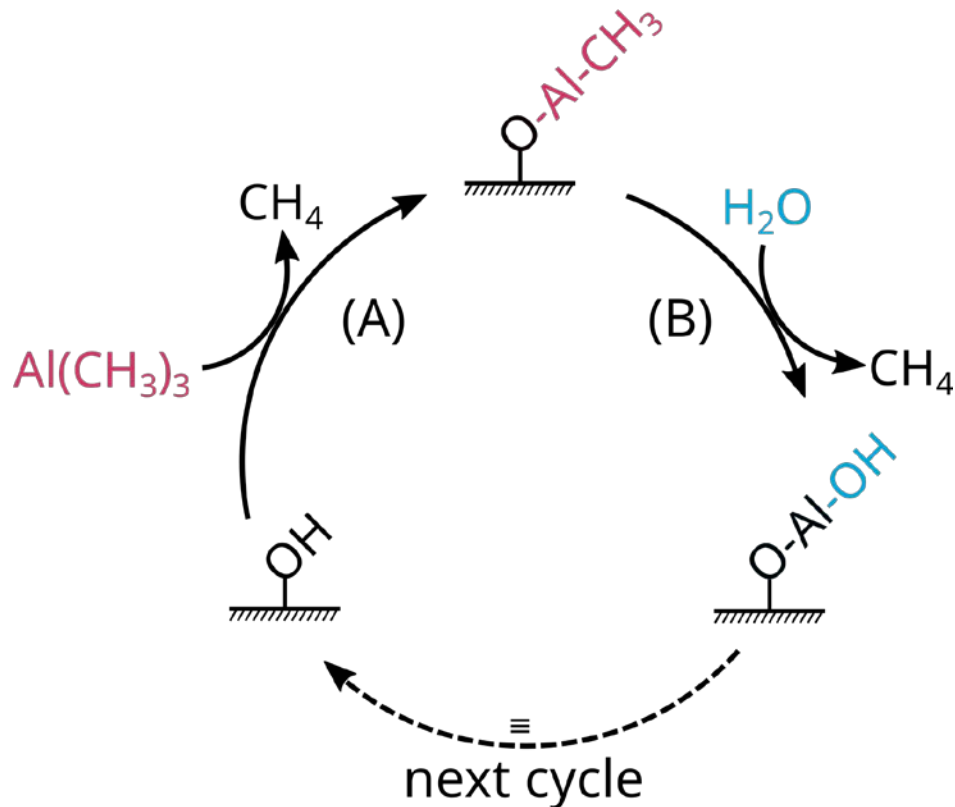
$$\epsilon_2(\omega) = \epsilon_\infty - \frac{\omega_p^2}{\omega^2 - i\omega/\tau_D} + \sum_{j=1}^n \frac{f_j \omega_p^2}{\omega_{0j}^2 - \omega^2 + i\gamma_j \omega}$$

Drude
term
(resistivity)

Lorentz
terms

	Optical resistivity ($\mu\Omega$ cm)	FPP resistivity ($\mu\Omega$ cm)	Bulk resistivity ($\mu\Omega$ cm)
Pt (53 nm)	12.6	13.0 ± 0.2	10.4
Ru (90 nm)	32.8	18.0 ± 0.6	6.7
Pd (42 nm)	67.5	67 ± 1	10.5

ALD of Al_2O_3 [Case study]



Prototypical ALD process

Precursor: $\text{Al}(\text{CH}_3)_3$

Reactant: H_2O

Temperature: 25-400 °C

Simplified reaction scheme:

A - 1st Half Cycle

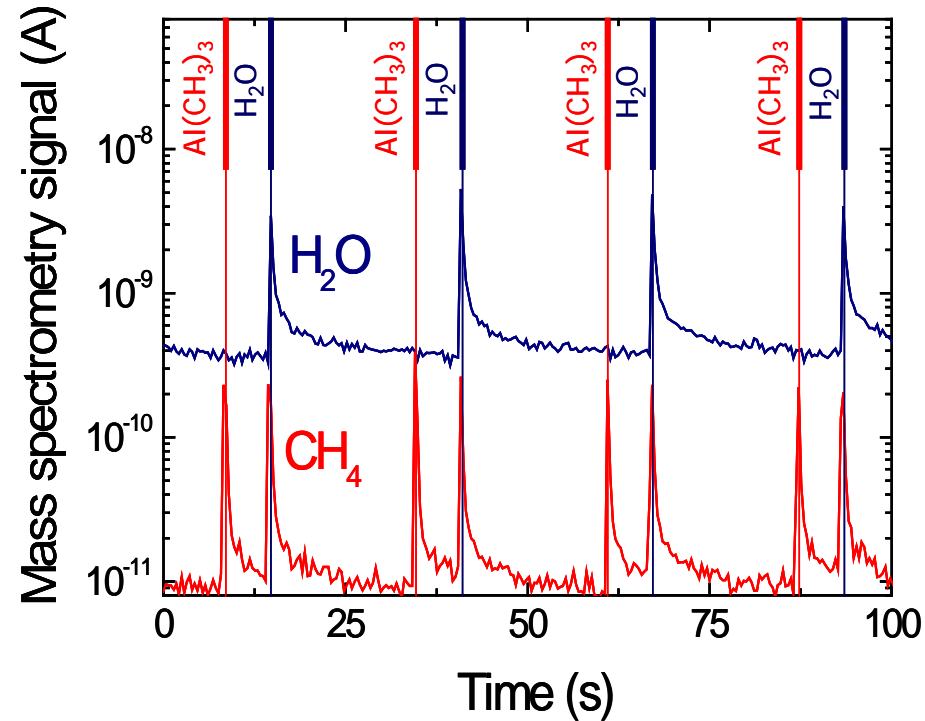
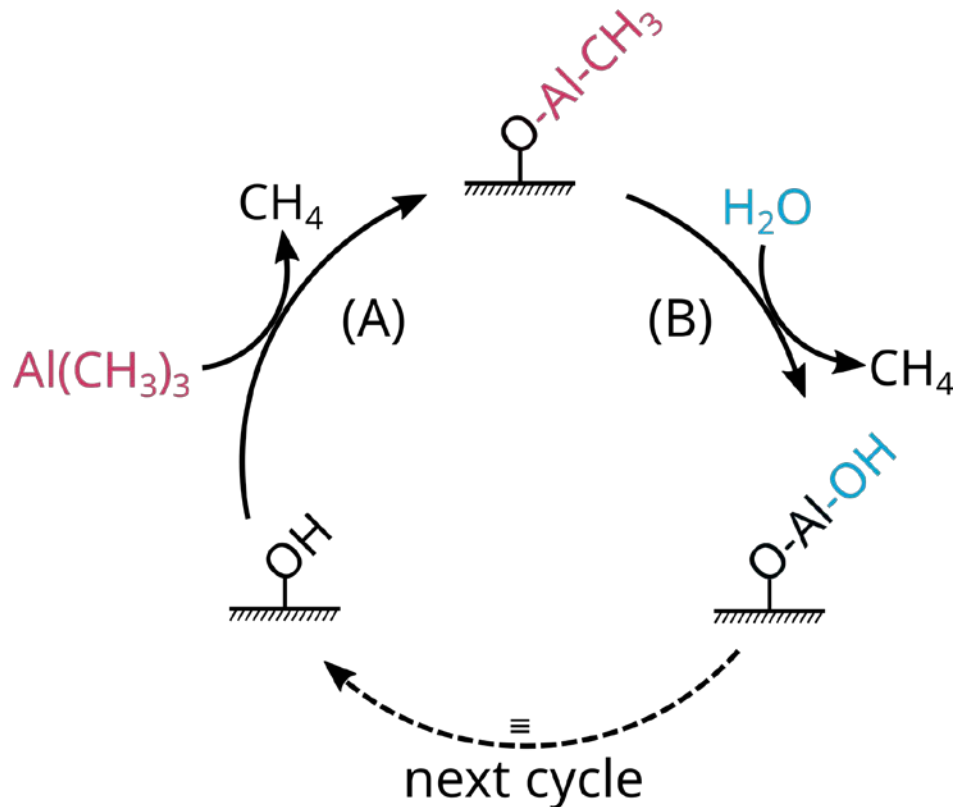


B - 2nd Half Cycle



Mass spectrometry — Reaction products (Al_2O_3)

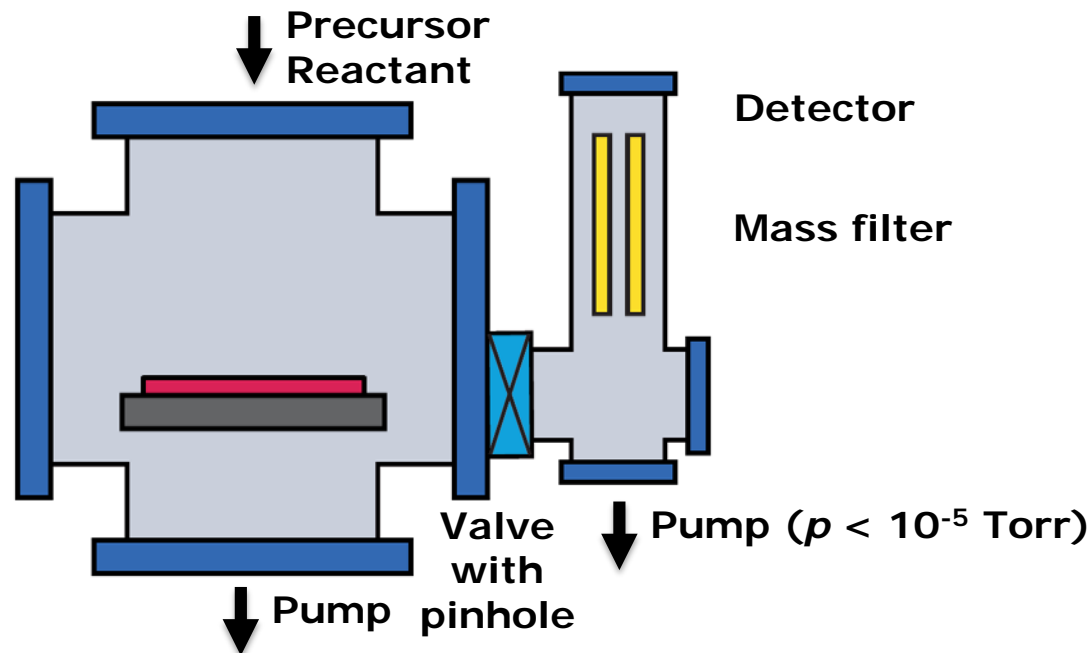
Gas phase **reaction products**



$\text{Al}(\text{CH}_3)_3$ dosing: **CH_4**

H_2O dosing: **CH_4**

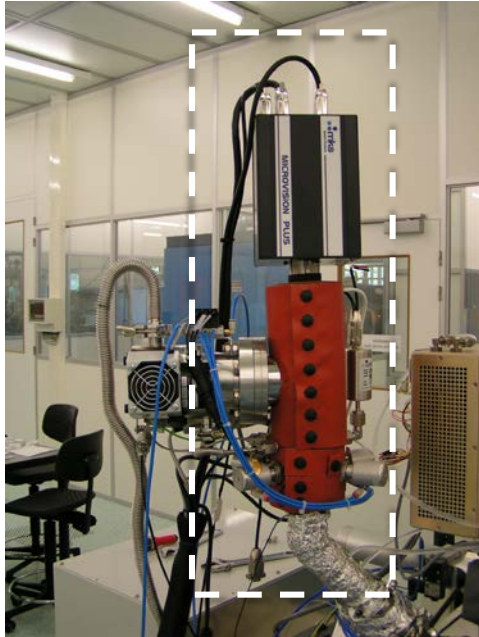
Quadrupole mass spectrometry (QMS)



Ionization of gas extracted from the reactor & mass filtering of the ions

- ▲ • Easy-to-implement on all types of reactors (with differential pumping)
- ▲ • Wide range of species can be detected (but heavy masses difficult)
- ▲ ▼ • All reaction products measured (not only from substrate)
- ▼ • QMS cracks molecules into fragments complicating data interpretation

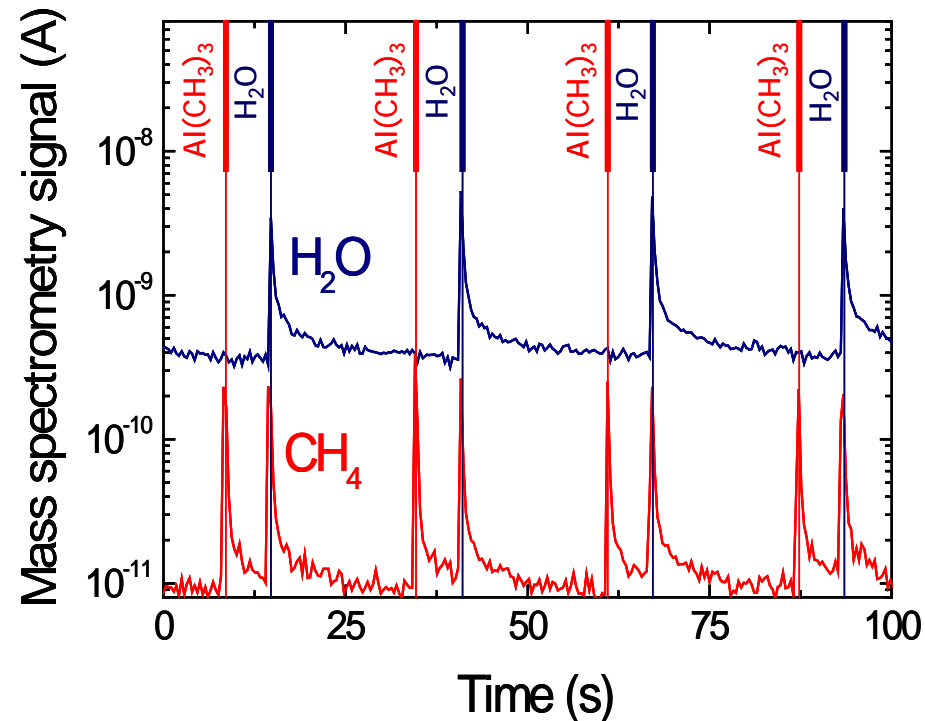
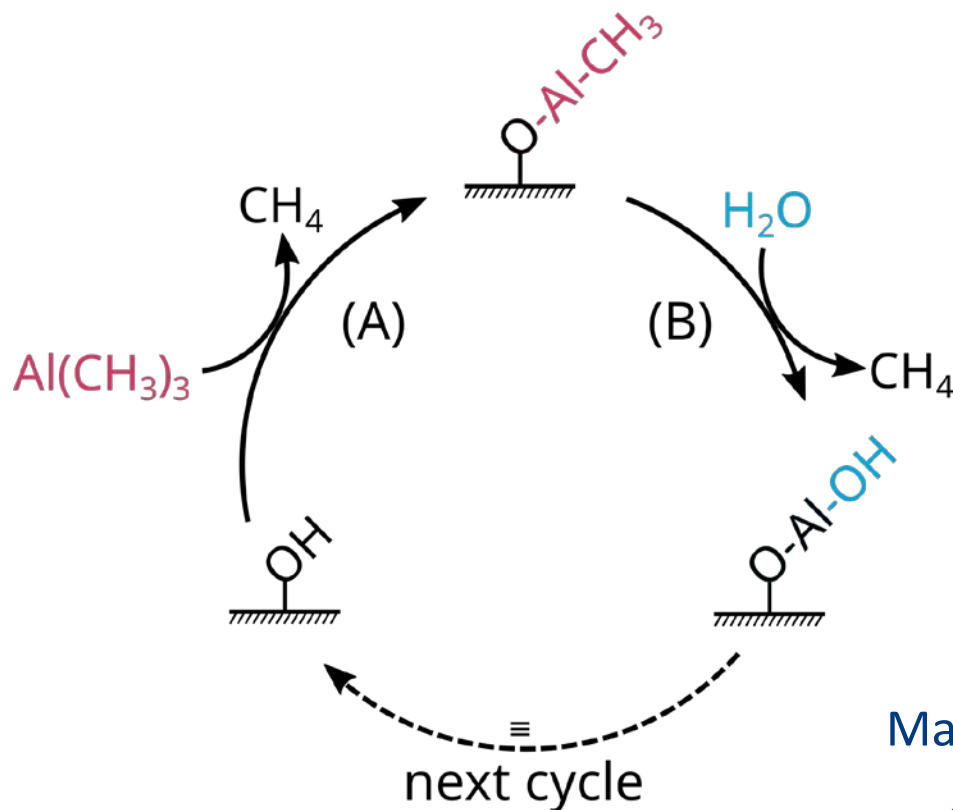
Quadrupole mass spectrometry (QMS)



Ionization of gas extracted from the reactor & mass filtering of the ions

- ▲ • Easy-to-implement on all types of reactors (with differential pumping)
- ▲ • Wide range of species can be detected (but heavy masses difficult)
- ▲ ▼ • All reaction products measured (not only from substrate)
- ▼ • QMS cracks molecules into fragments complicating data interpretation

Mass spectrometry — Reaction products (Al_2O_3)

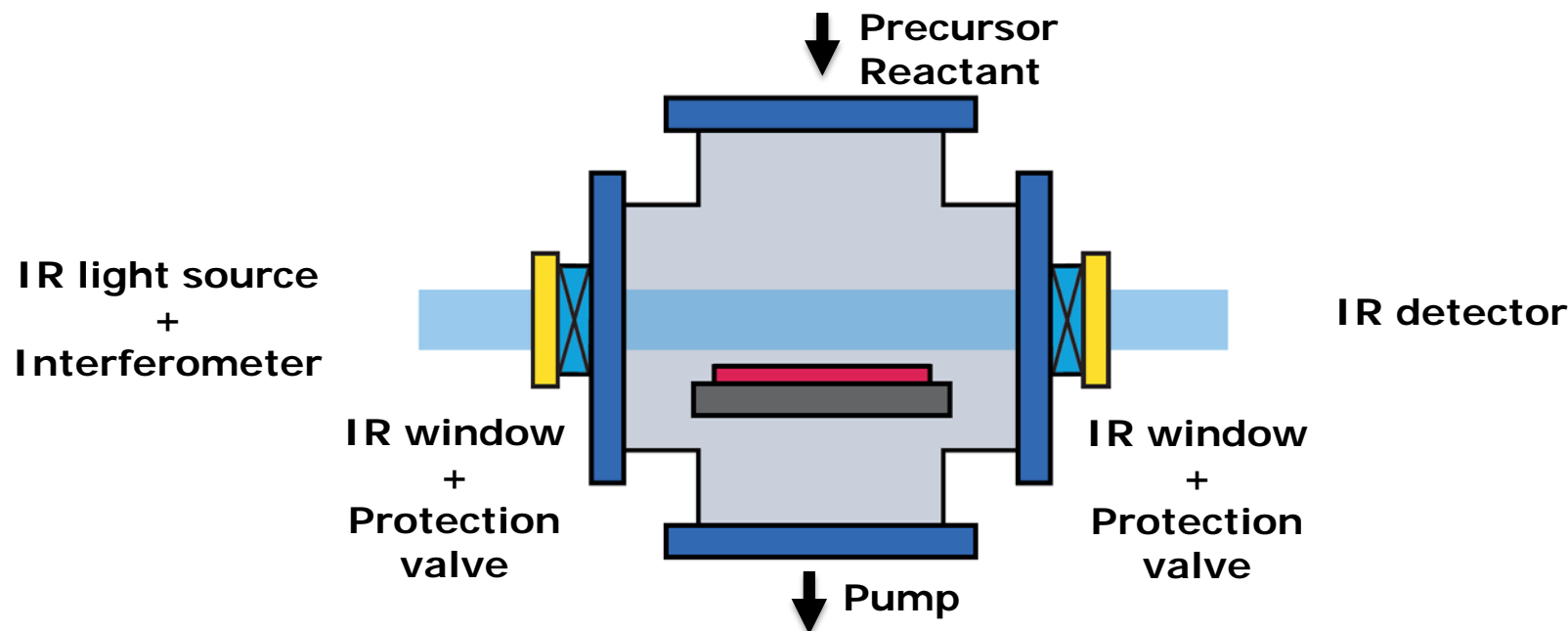


Mass spectrometry probes **mass/charge ratios**

CH_4 probed at **16 (CH_4^+)**; 15 (CH_3^+), etc.

H_2O probed at 18 (H_2O^+); 17 (OH^+); **16 (O^+)**

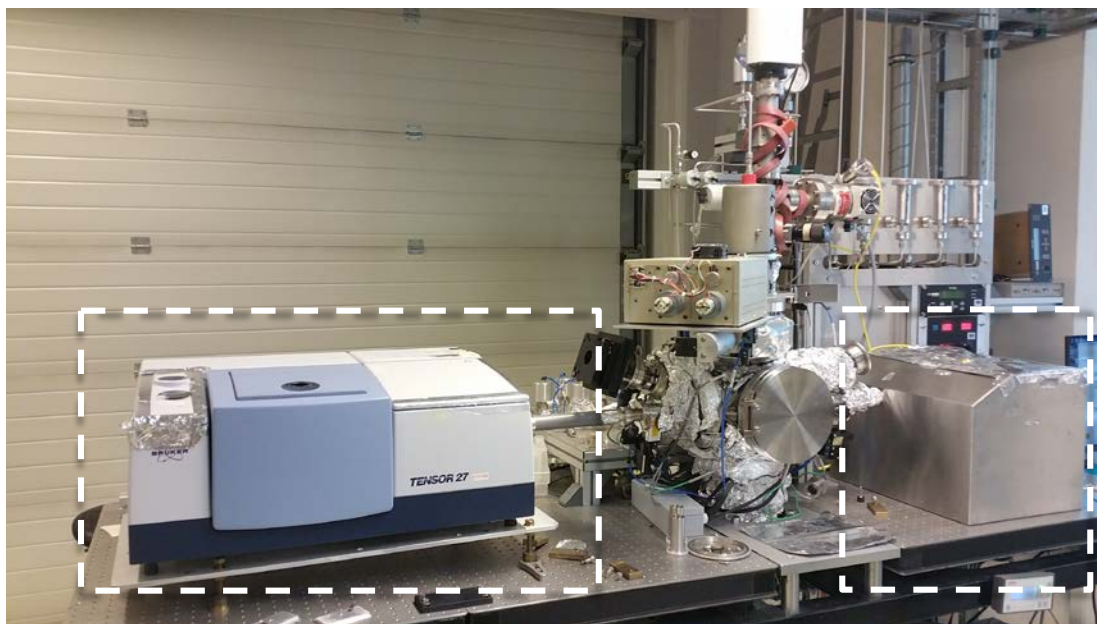
Gas-phase infrared spectroscopy (FTIR)



Absorption of infrared light (from FTIR interferometer) by rovibrational transitions

- ▲ . Calibration is quite straightforward to yield absolute densities
- ▲▼ . High sensitivity for certain species but not all species can be detected
- ▲▼ . All reaction products measured (not only from substrate)
- ▼ . Confinement of reaction products might be necessary for sufficient S/N ratio

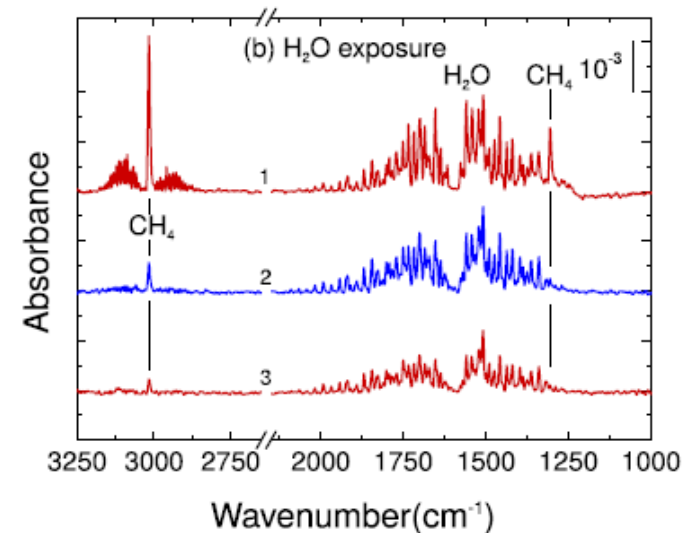
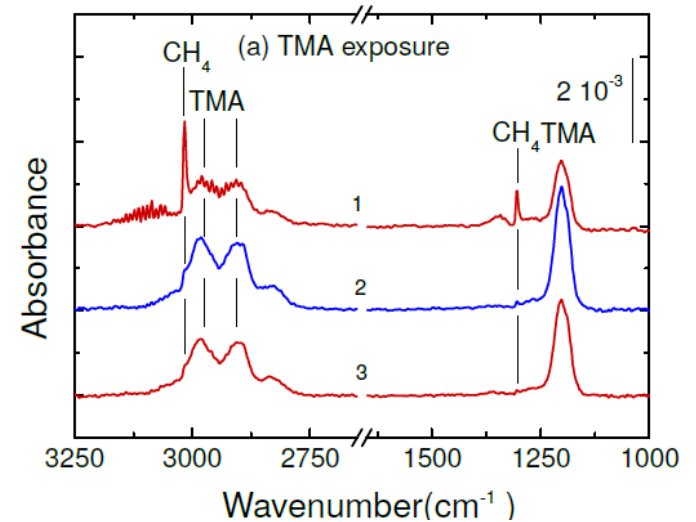
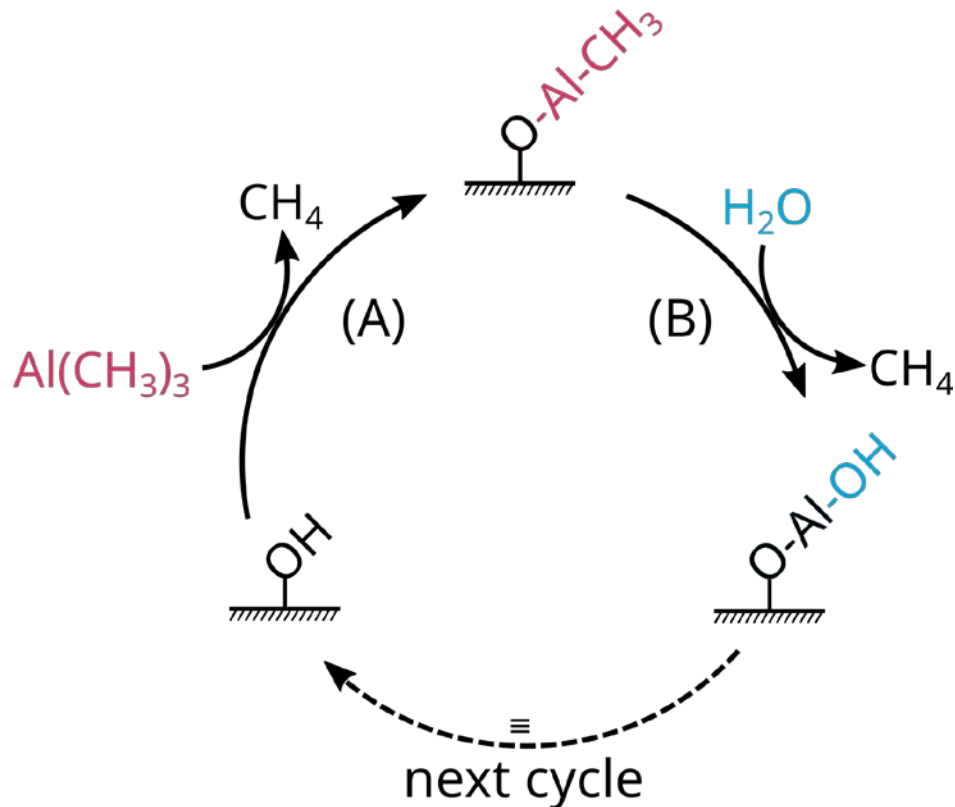
Gas-phase infrared spectroscopy (FTIR)



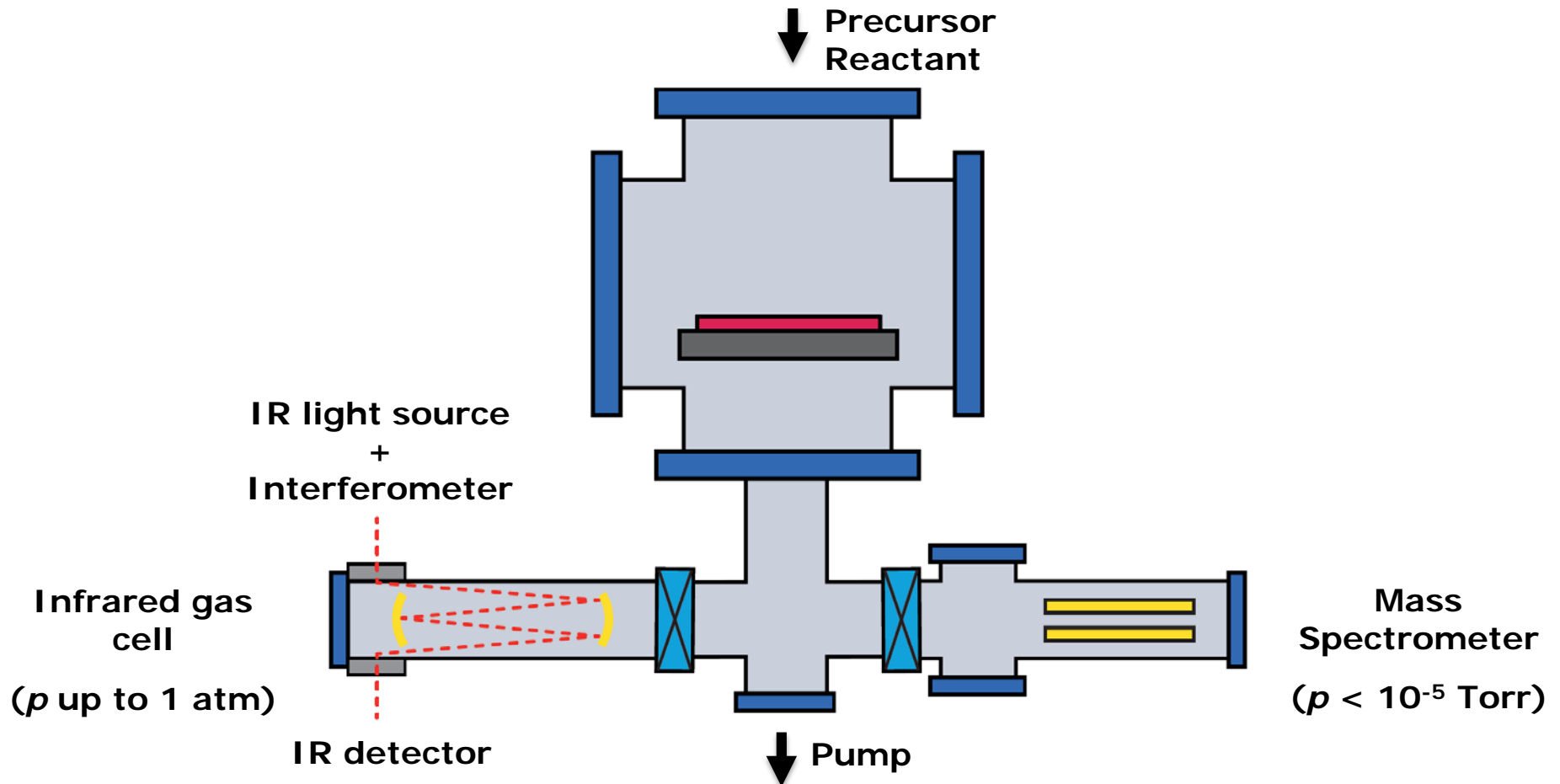
Absorption of infrared light (from FTIR interferometer) by rovibrational transitions

- ▲ . Calibration is quite straightforward to yield absolute densities
- ▲▼ . High sensitivity for certain species but not all species can be detected
- ▲▼ . All reaction products measured (not only from substrate)
- ▼ . Confinement of reaction products might be necessary for sufficient S/N ratio

Gas-phase FTIR — Reaction products (Al_2O_3)

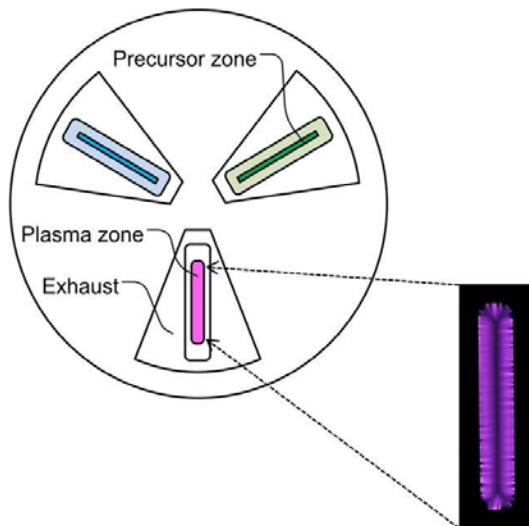
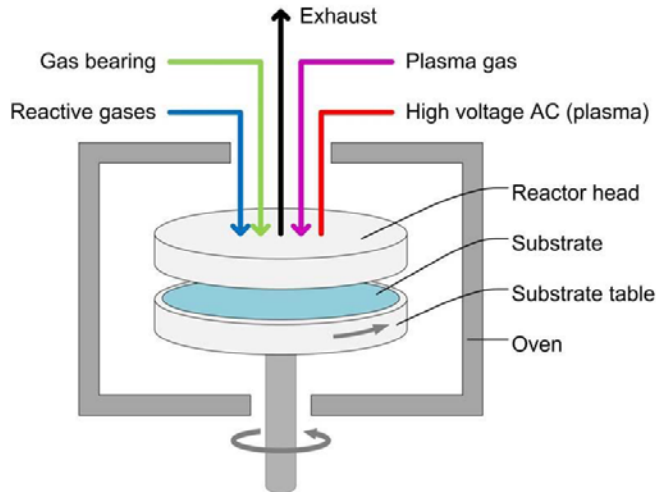


QMS and gas-phase FTIR installed in exhaust

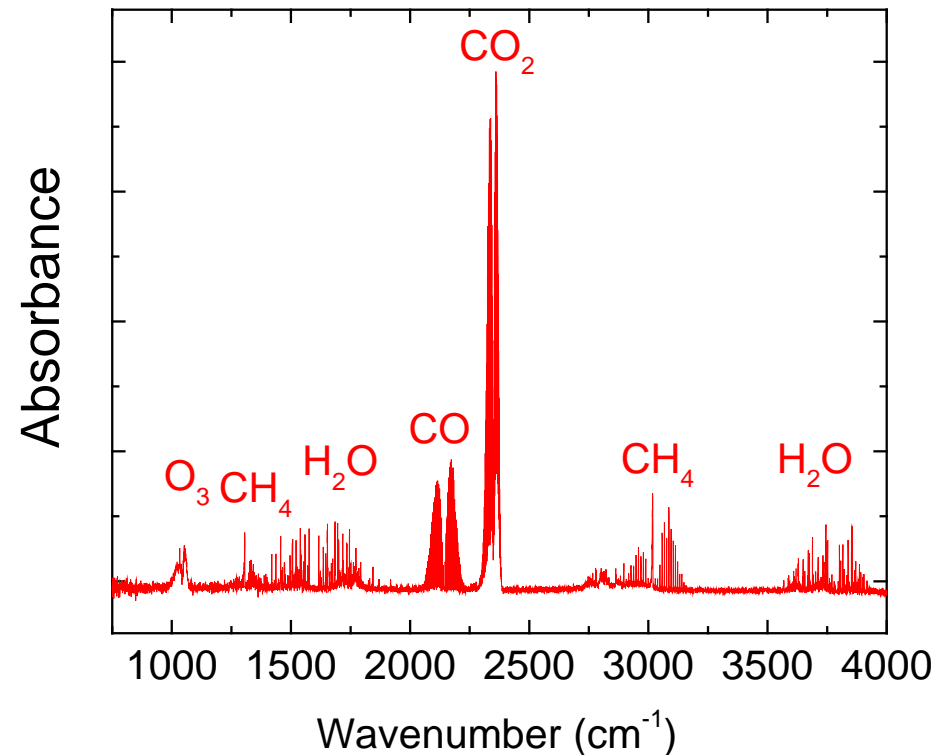


Can quite easily be implemented in **industrial (spatial)** ALD equipment

Gas-phase FTIR in exhaust of spatial ALD setup

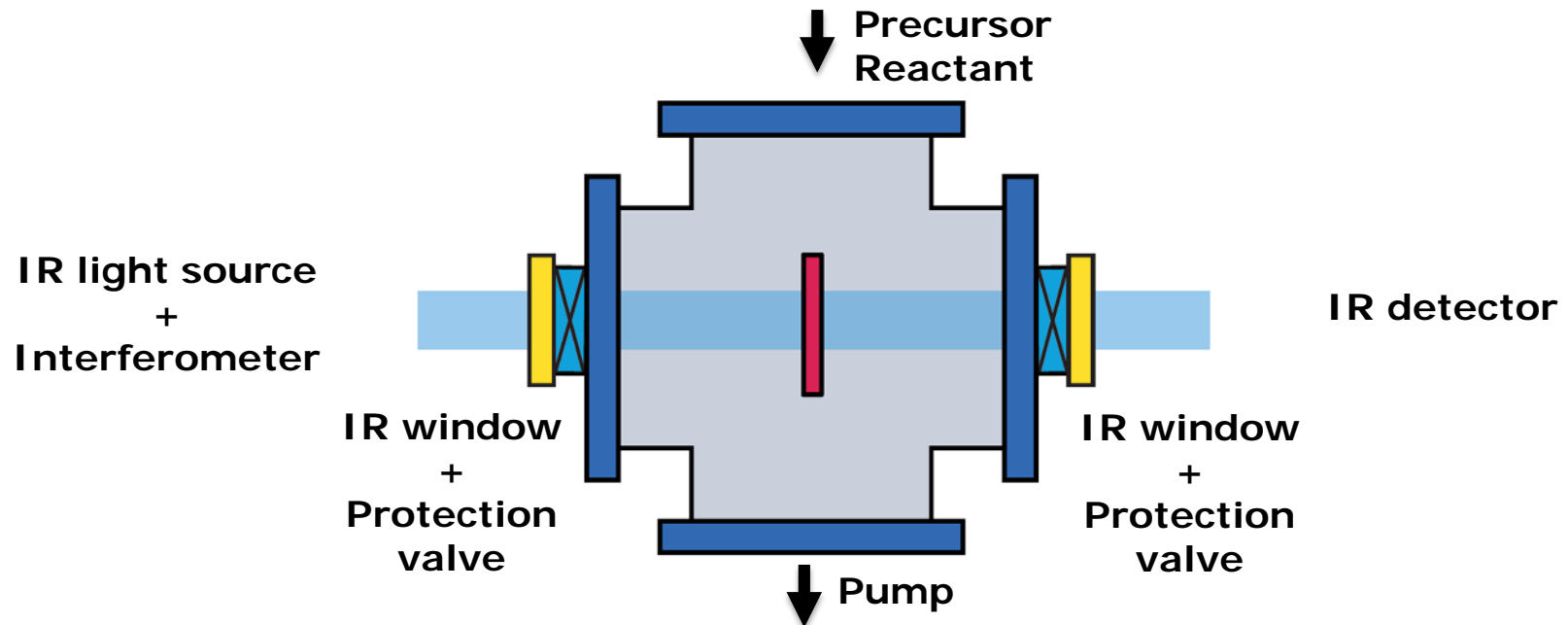


Spectrum of O_2 plasma reactant step during plasma-assisted spatial ALD of Al_2O_3



Reaction products:
 O_3 , combustion products and CH_4

Surface infrared spectroscopy (FTIR)

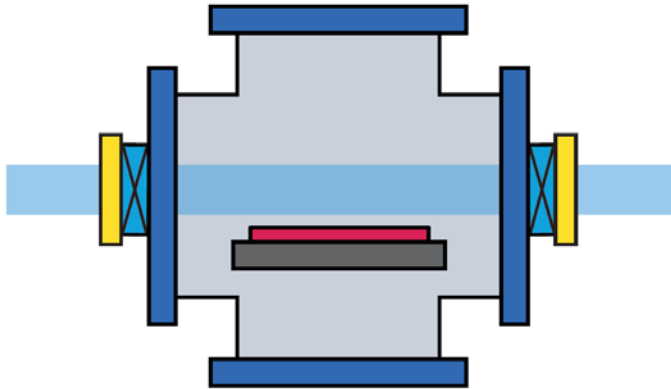


Absorption of infrared light by vibrational transitions by (surface) groups

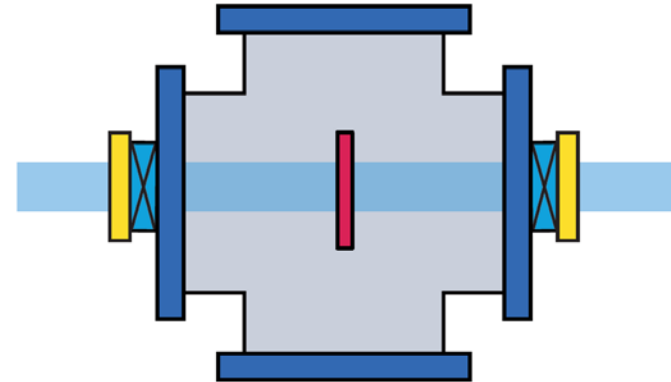
- ▲ . Direct measurement of surface groups created, removed or incorporated
- ▲▼ . Probes only surface groups which are changing every (half-)cycle
- ▼ . Poor S/N ratio for some species – long integration times required
- ▼ . Requires dedicated reactor with optical access and IR-transparent substrate

Various configurations infrared spectroscopy

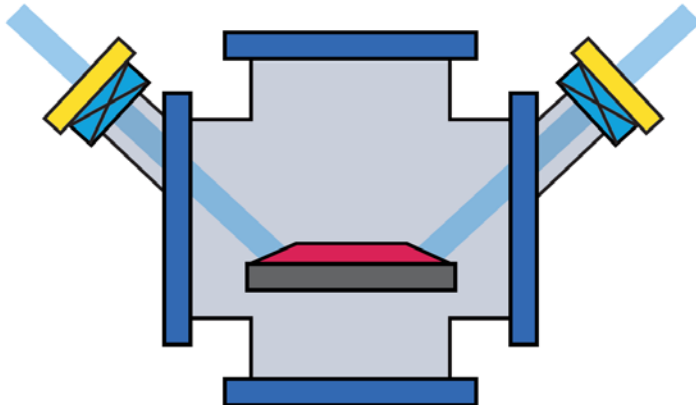
Gas phase species



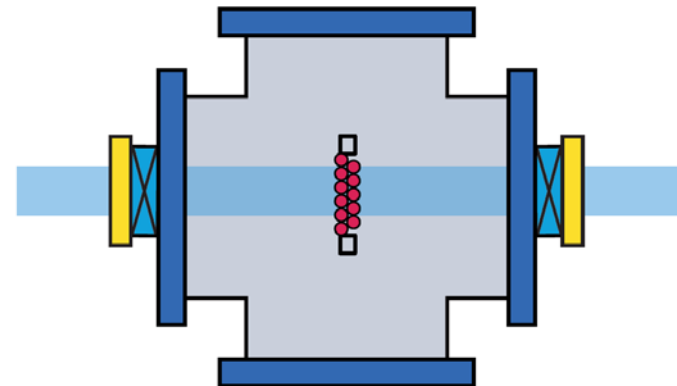
Surface species - wafer



Surface species – ATR element
(multiple reflections at surface)



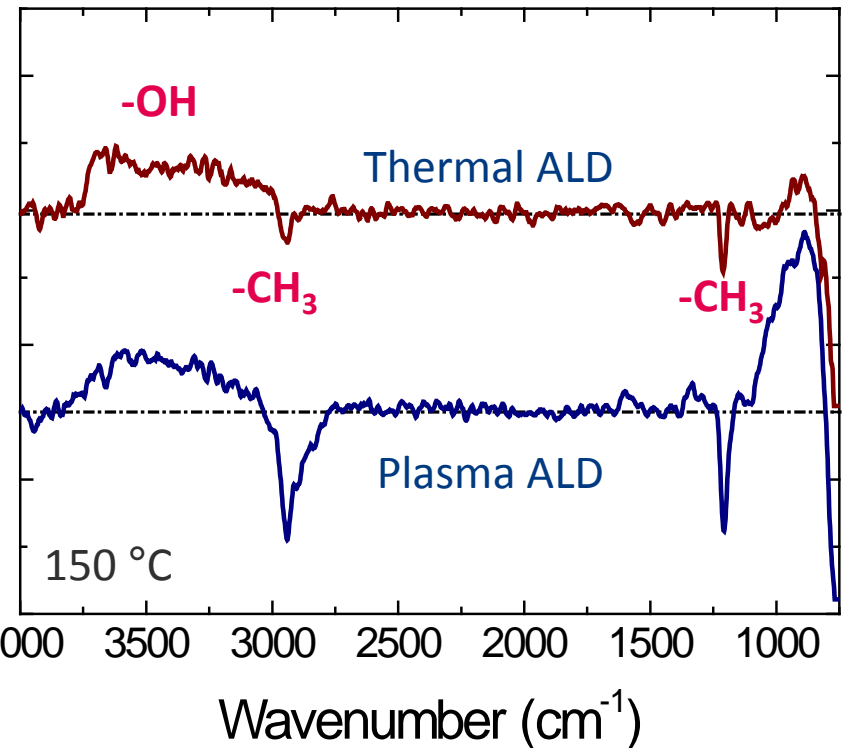
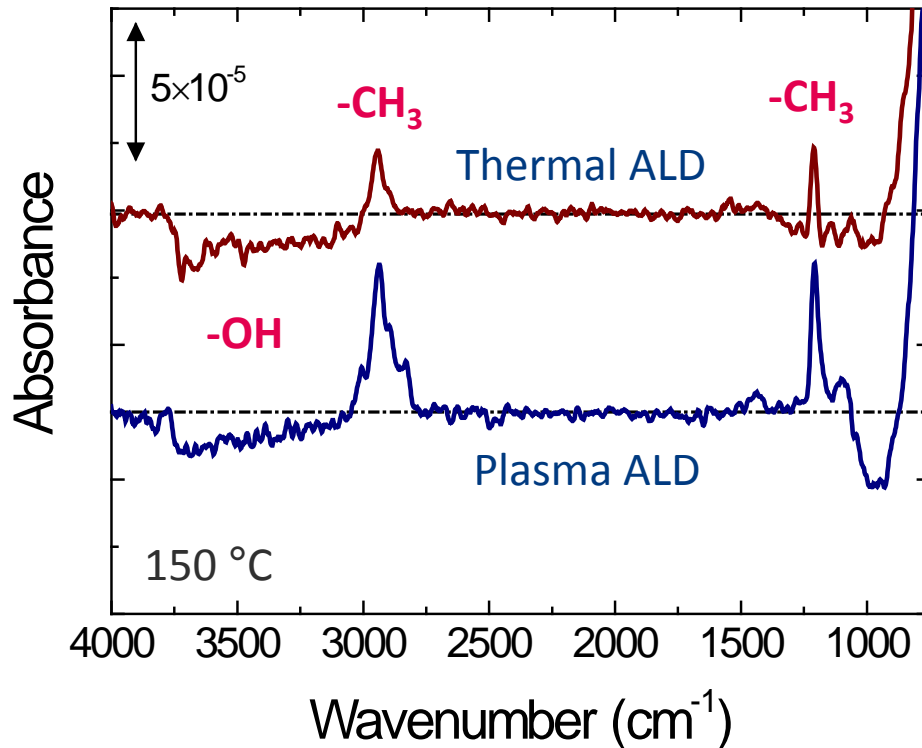
Surface species – particles
(enlarged surface area by particles)



Surface FTIR – Surface groups (Al_2O_3)

$\text{Al}(\text{CH}_3)_3$

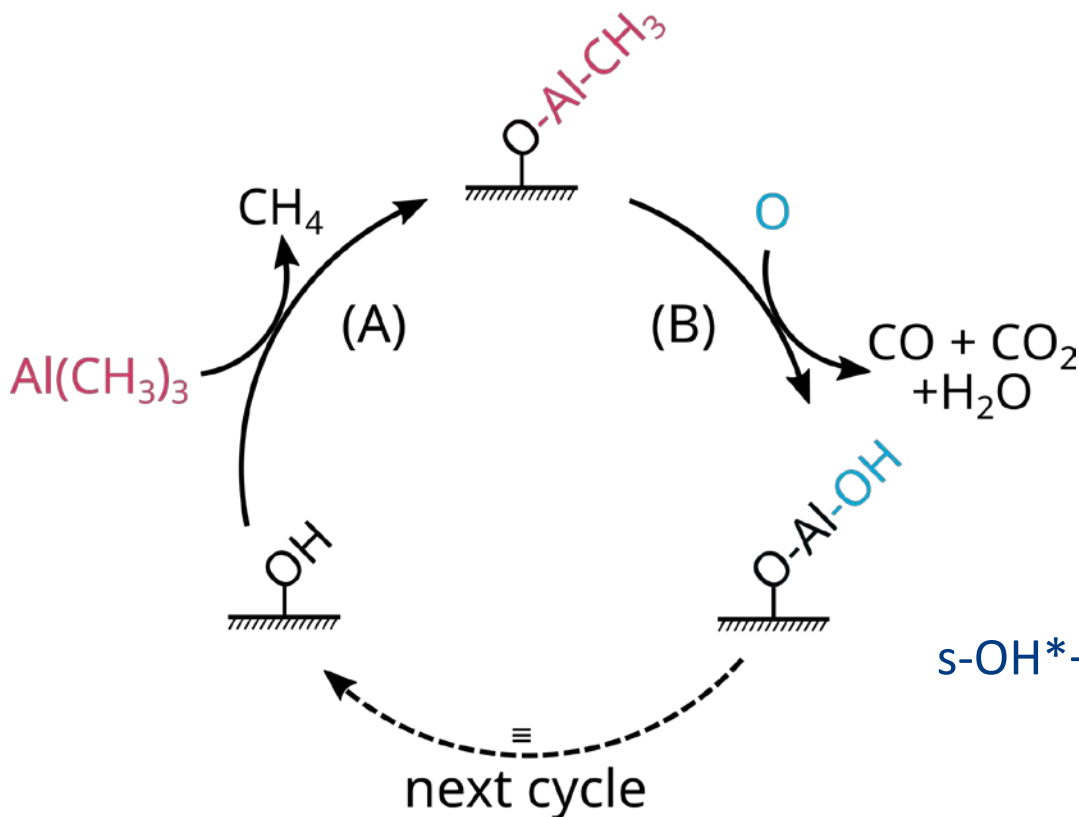
H_2O or O_2 plasma



Differential spectra: show changes per half cycle

$-\text{CH}_3$ and $-\text{OH}$ are surface groups for both thermal and plasma ALD

Plasma-enhanced ALD of Al_2O_3 [Case study]



Precursor: $\text{Al}(\text{CH}_3)_3$

Reactant: O_2 plasma

Temperature: 25-400 °C

Simplified reaction scheme:

A - 1st Half Cycle



B - 2nd Half Cycle



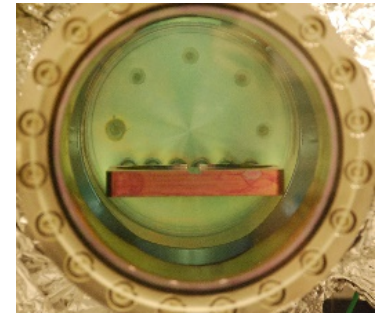
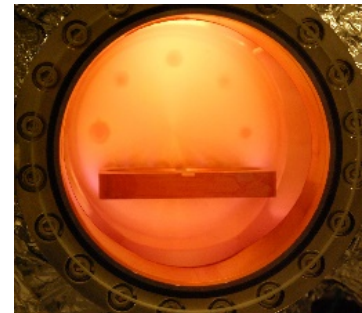
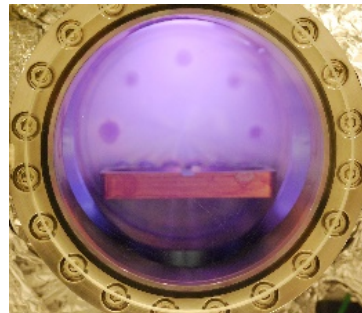
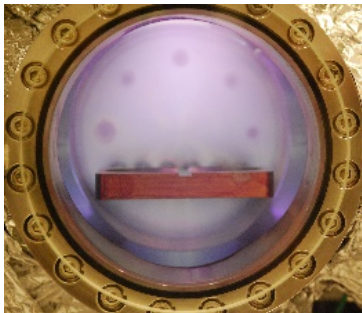
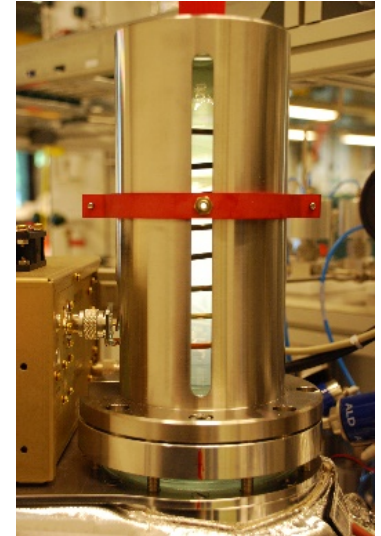
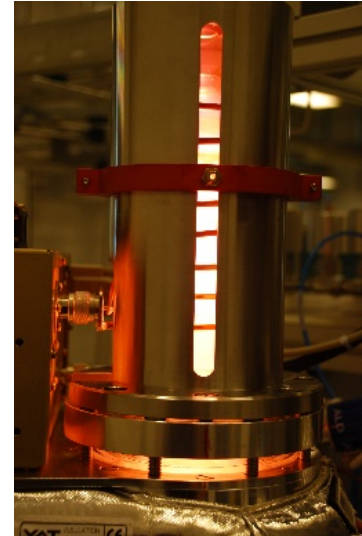
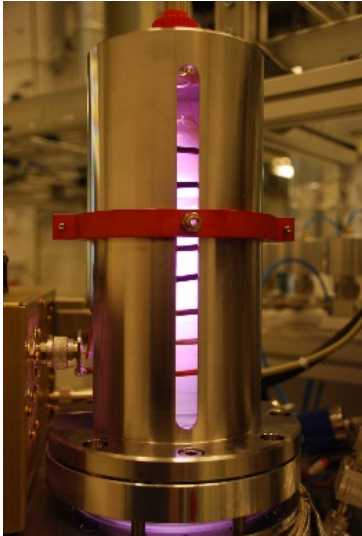
Plasma radiation – feed gas dependent

Ar

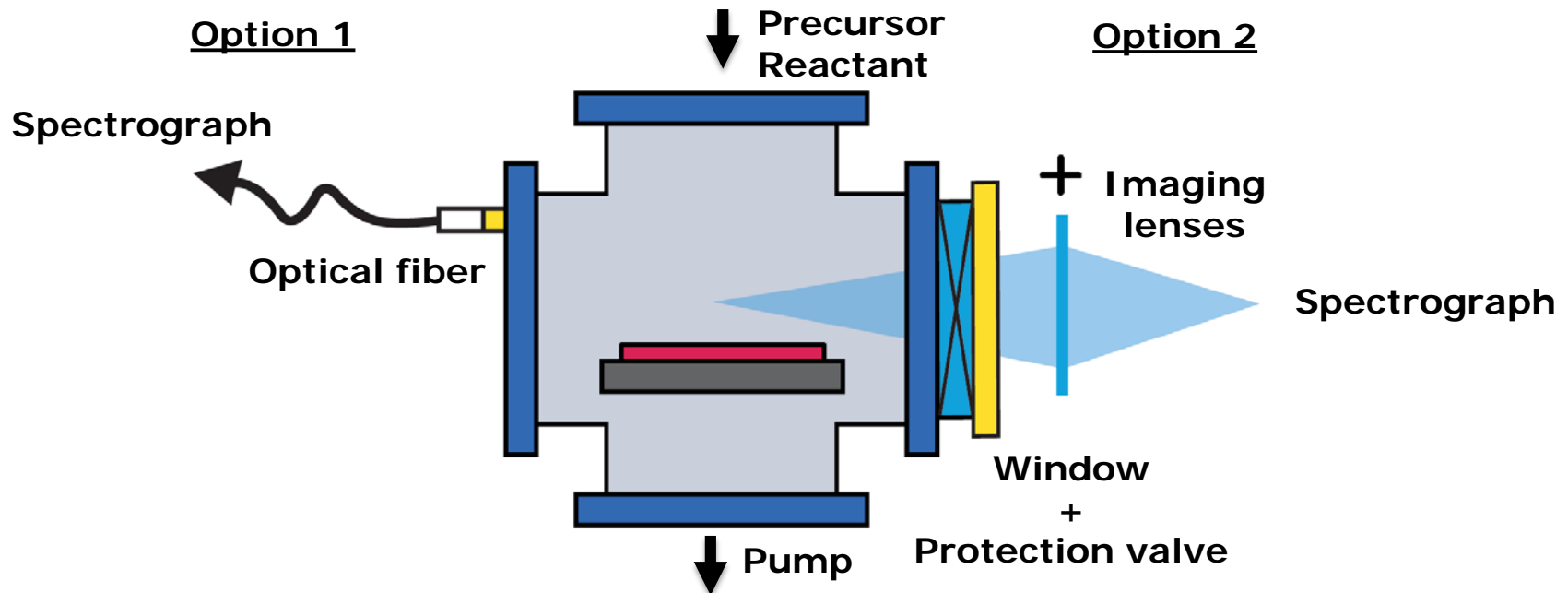
H₂

N₂

O₂



Optical emission spectroscopy (OES)



Measures (visible) radiation from excited species decaying to lower levels

- ▲ . Ideally suited for process monitoring of plasma-based processes
- ▲ . Extremely easy to implement & cheap
- ▼ . Yields only information about excited species – not ground state species
- ▼ . Typically yields very indirect and qualitative information

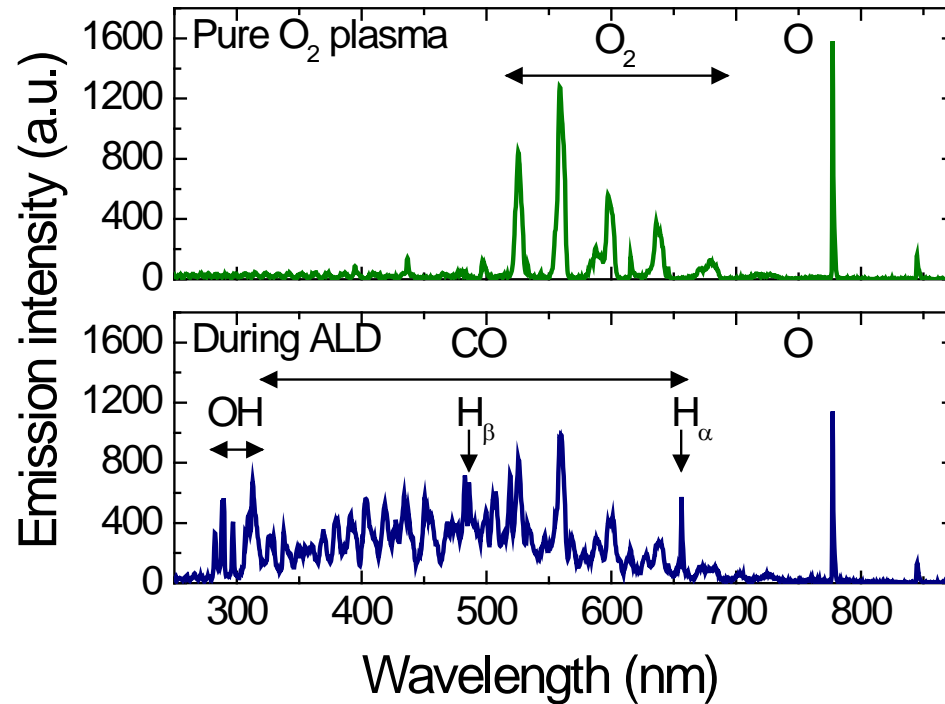
Optical emission spectroscopy (OES)



Measures (visible) radiation from excited species decaying to lower levels

- ▲ . Ideally suited for process monitoring of plasma-based processes
- ▲ . Extremely easy to implement & cheap
- ▼ . Yields only information about excited species – not ground state species
- ▼ . Typically yields very indirect and qualitative information

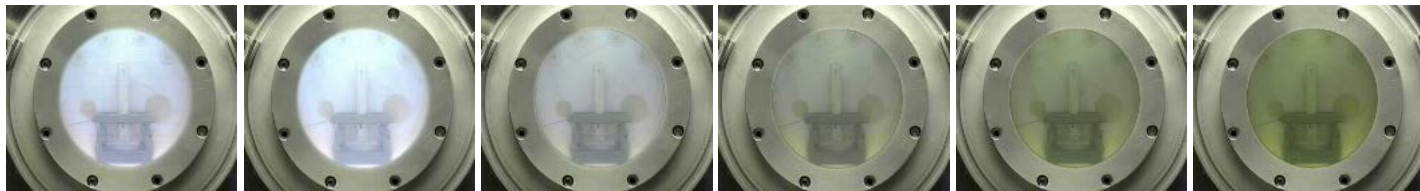
Optical emission spectroscopy – Plasma (Al_2O_3)



Plasma half-cycle

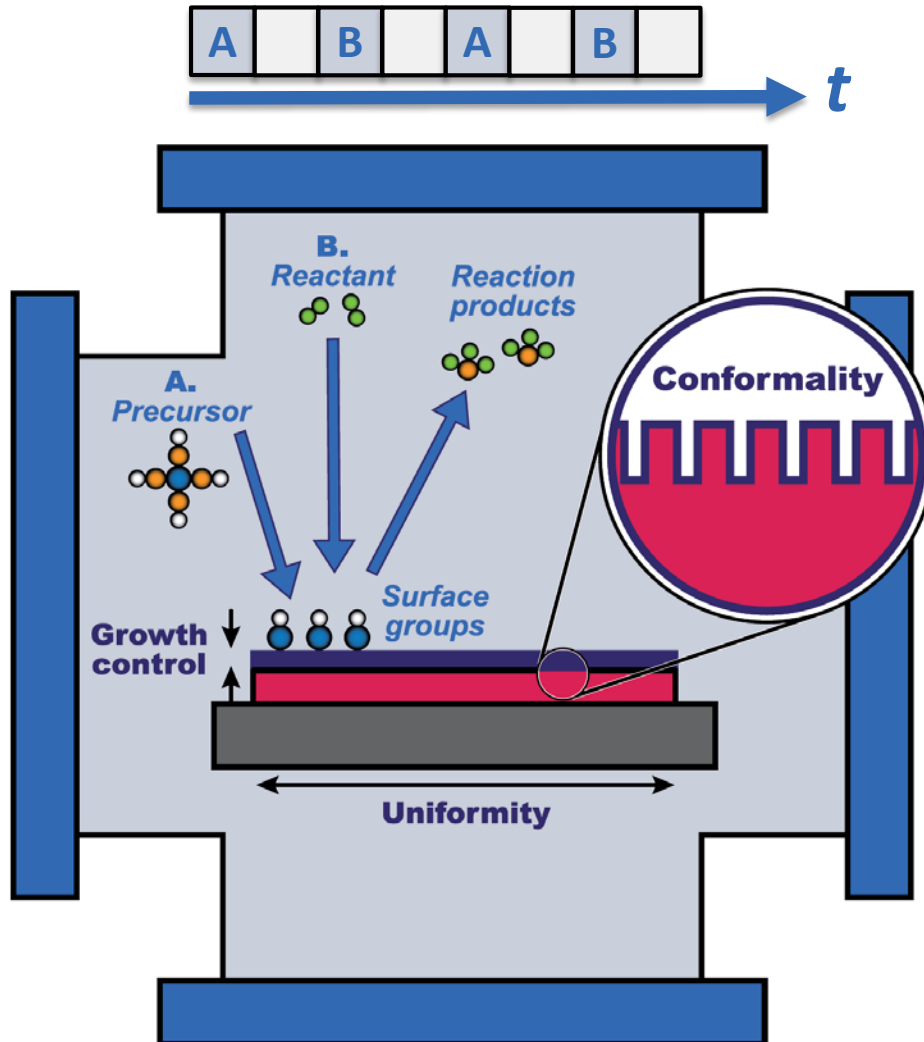


Plasma is “**disturbed**”
by reaction products



— t: — 0 s — 0.4 s — 0.8 s — 1.2 s — 1.6 s — 2.0 s —→

Atomic layer deposition (ALD)



Discussed **next**:

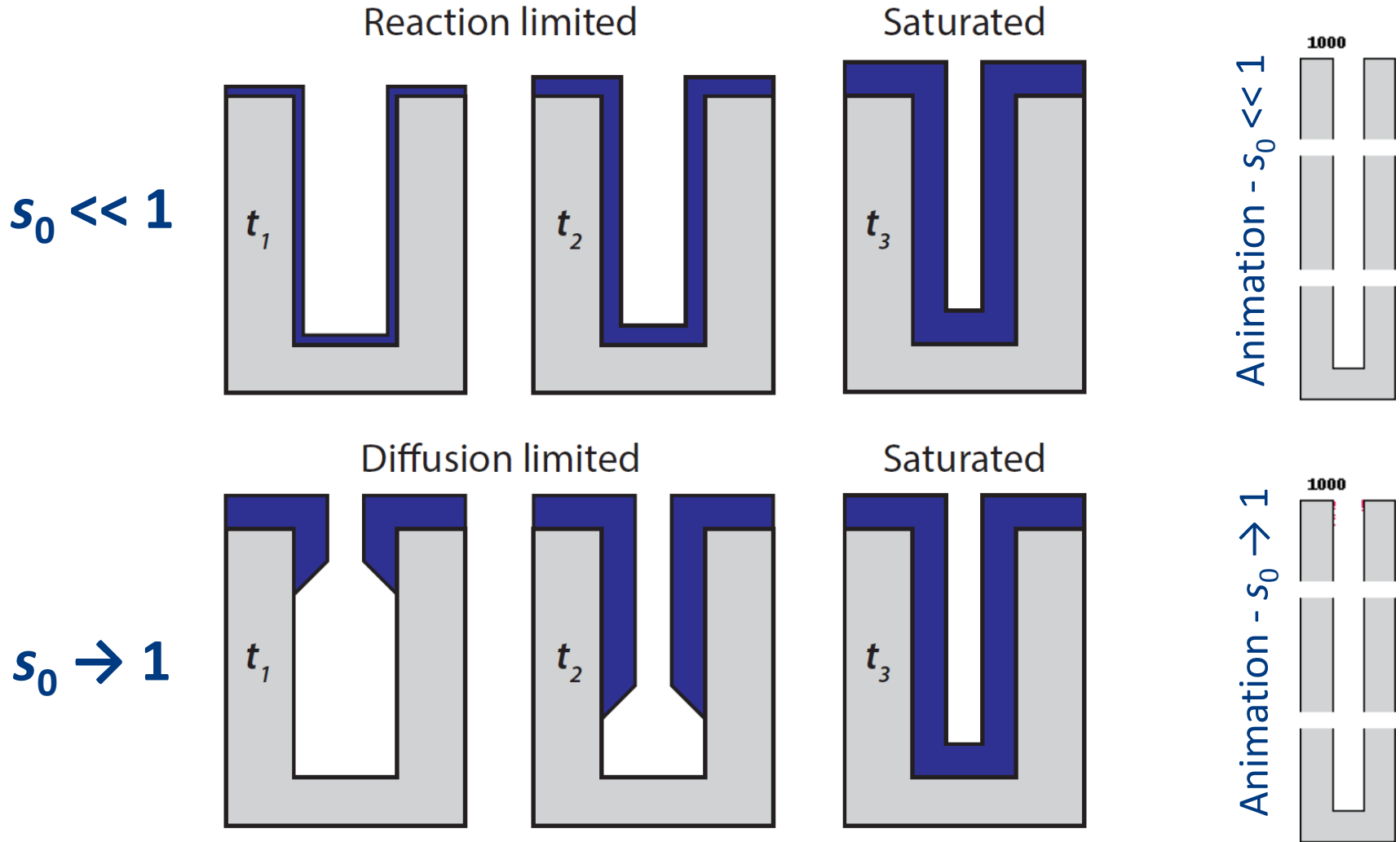
ALD merits:

- **Conformality**
- **Uniformity**
- **Growth control**

Advanced methods:

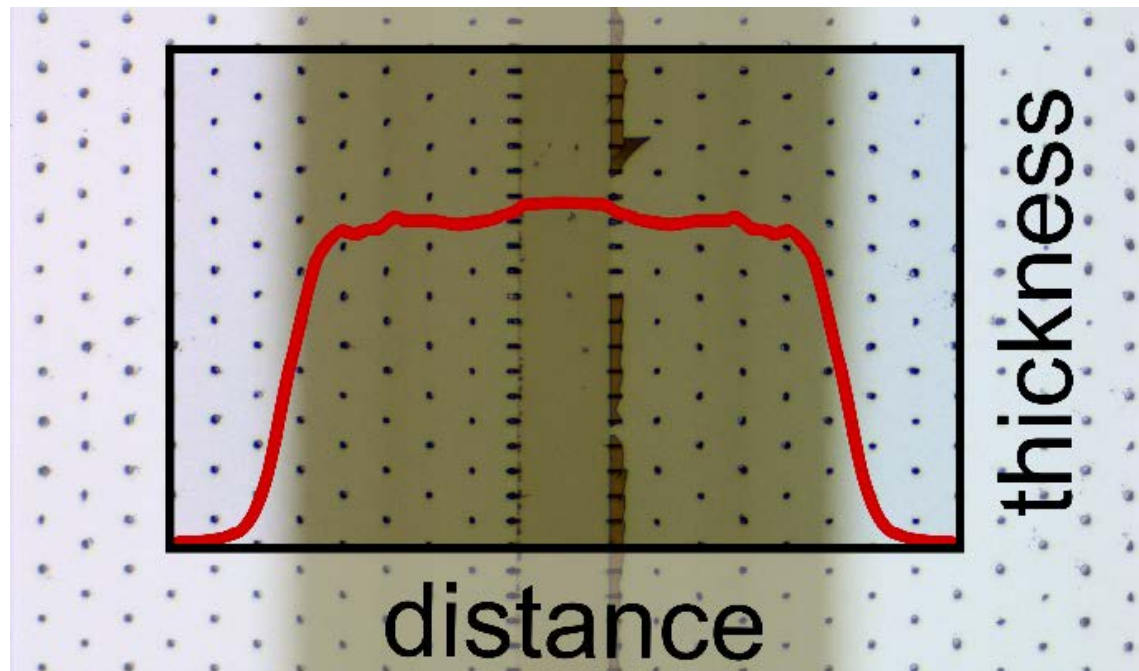
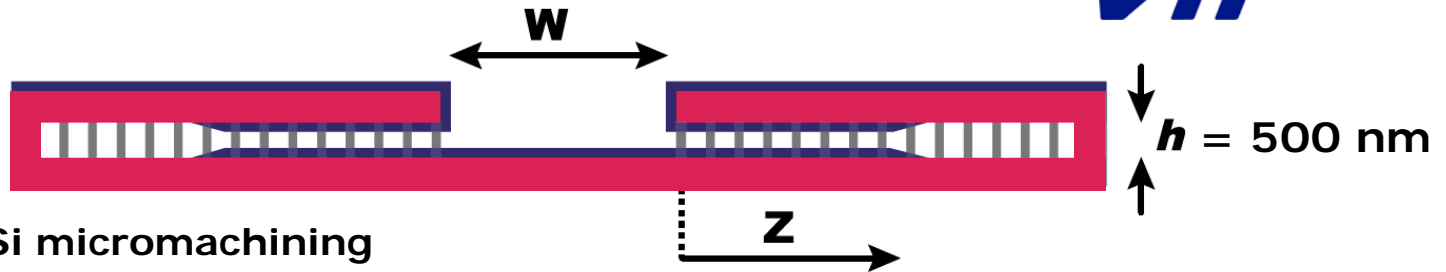
- **Sum-frequency generation**
- **Adsorption calorimetry**

Conformality – Reaction- vs. diffusion-limited



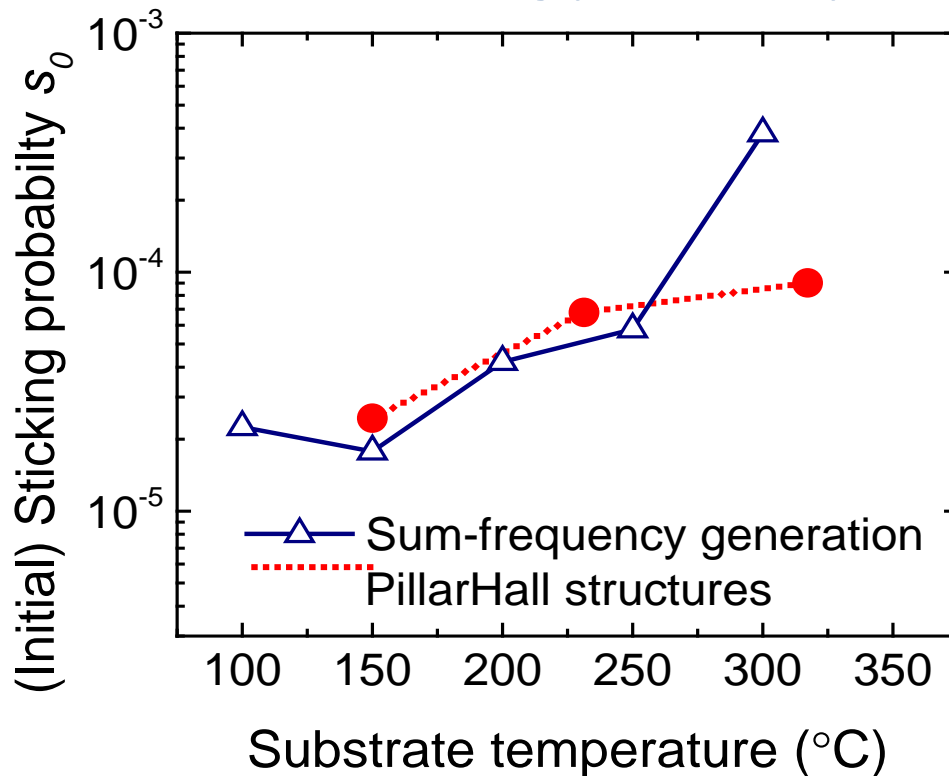
Conformality test structures

PillarHall™ LHAR structures

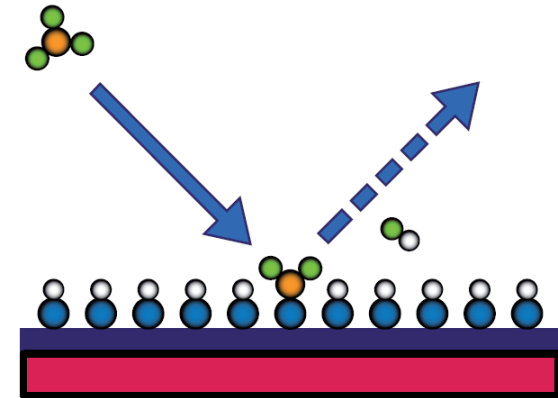


Conformality tests – sticking probability (Al_2O_3)

Sticking probability of H_2O during H_2O step



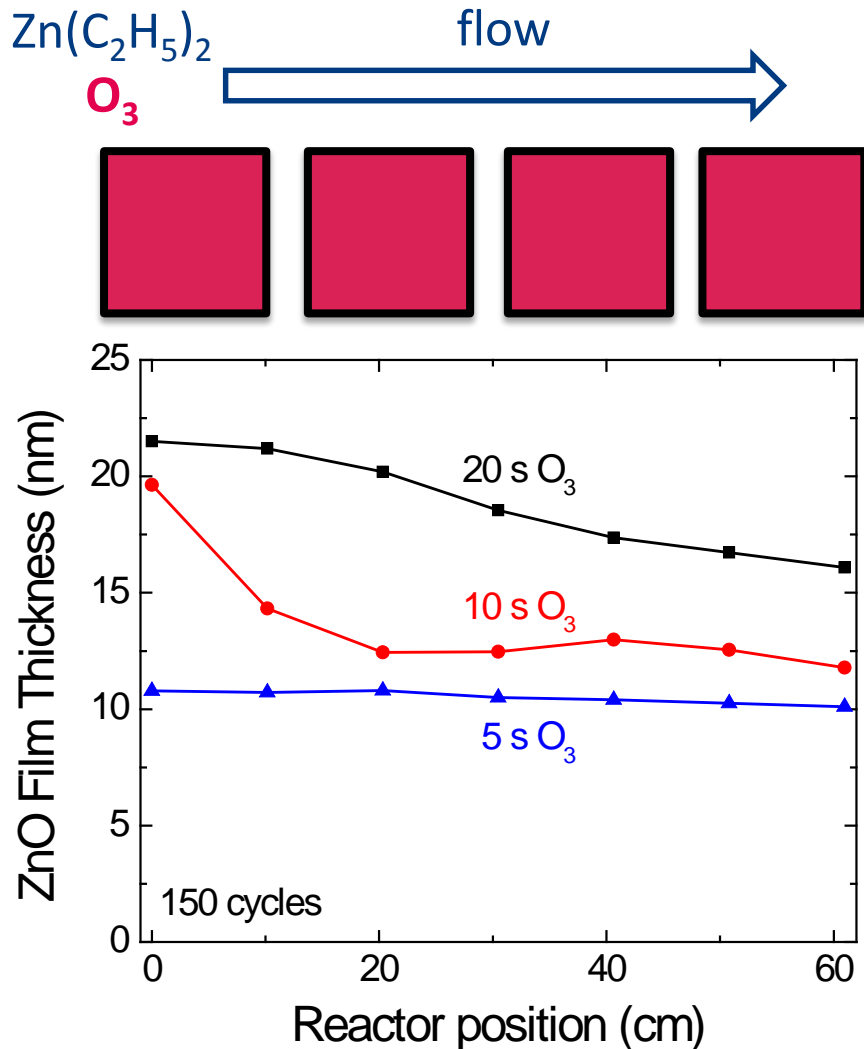
Initial sticking probability s_0



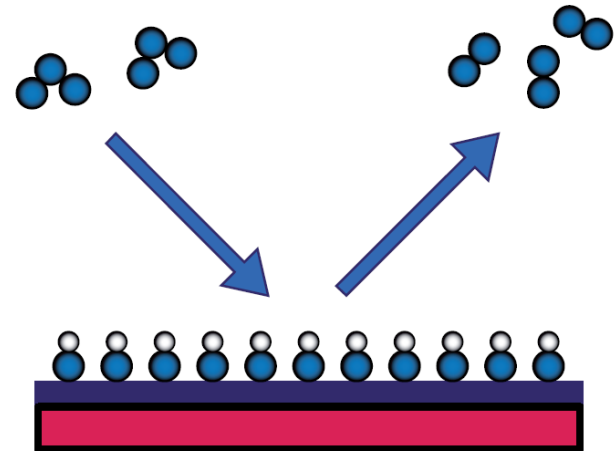
Good agreement with sum-frequency generation (SFG, see later)

Sticking probability of H_2O $< 10^{-4} \Rightarrow \text{H}_2\text{O}$ is **not very reactive** with $-\text{CH}_3$

Uniformity – O₃ surface loss (ZnO)

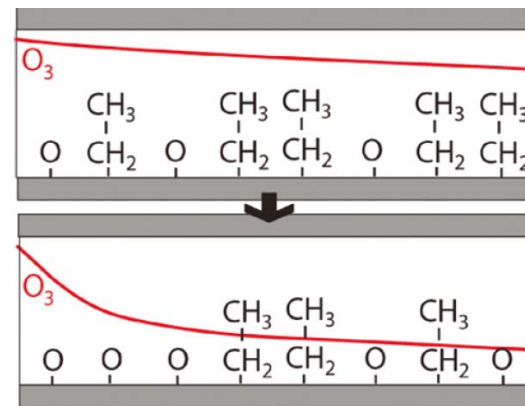
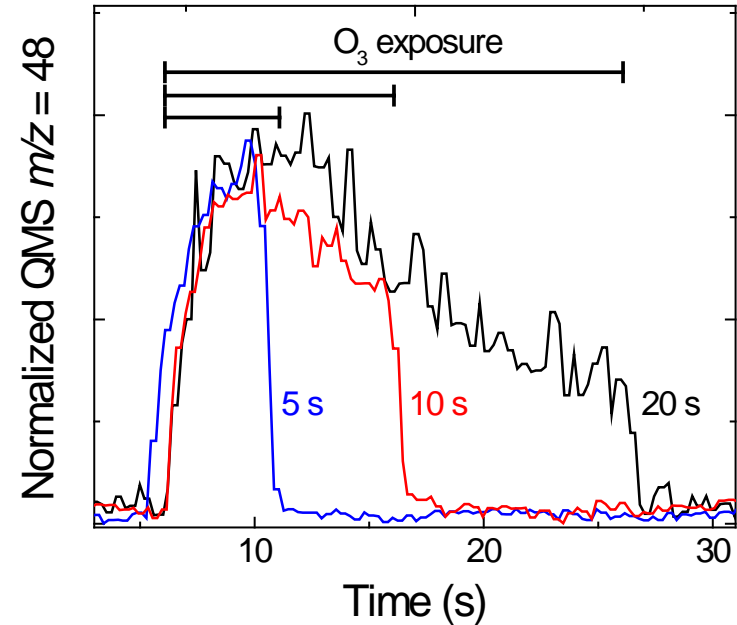
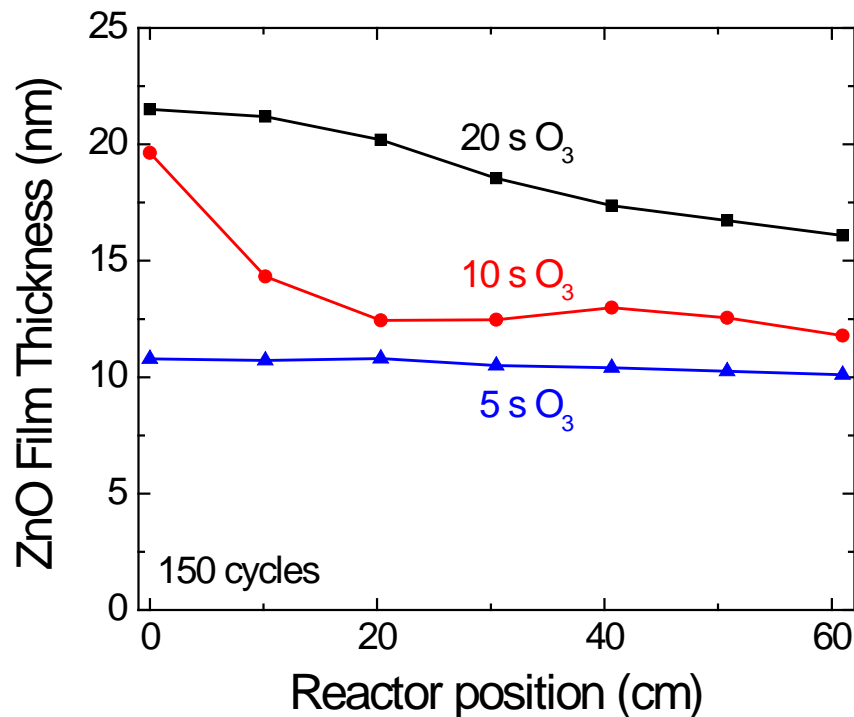
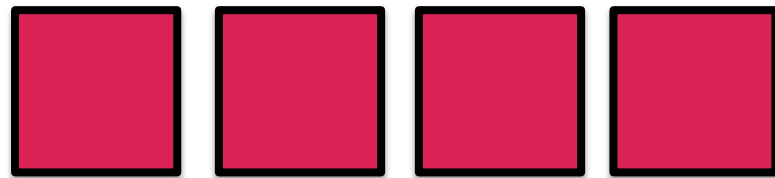


Surface loss/recombination of O₃



Depends on **surface termination**

Uniformity – O₃ surface loss (ZnO)



C₂H₅-term. surface
Low O₃ loss

ZnO surface
High O₃ loss

Growth control - initial growth on foreign surfaces

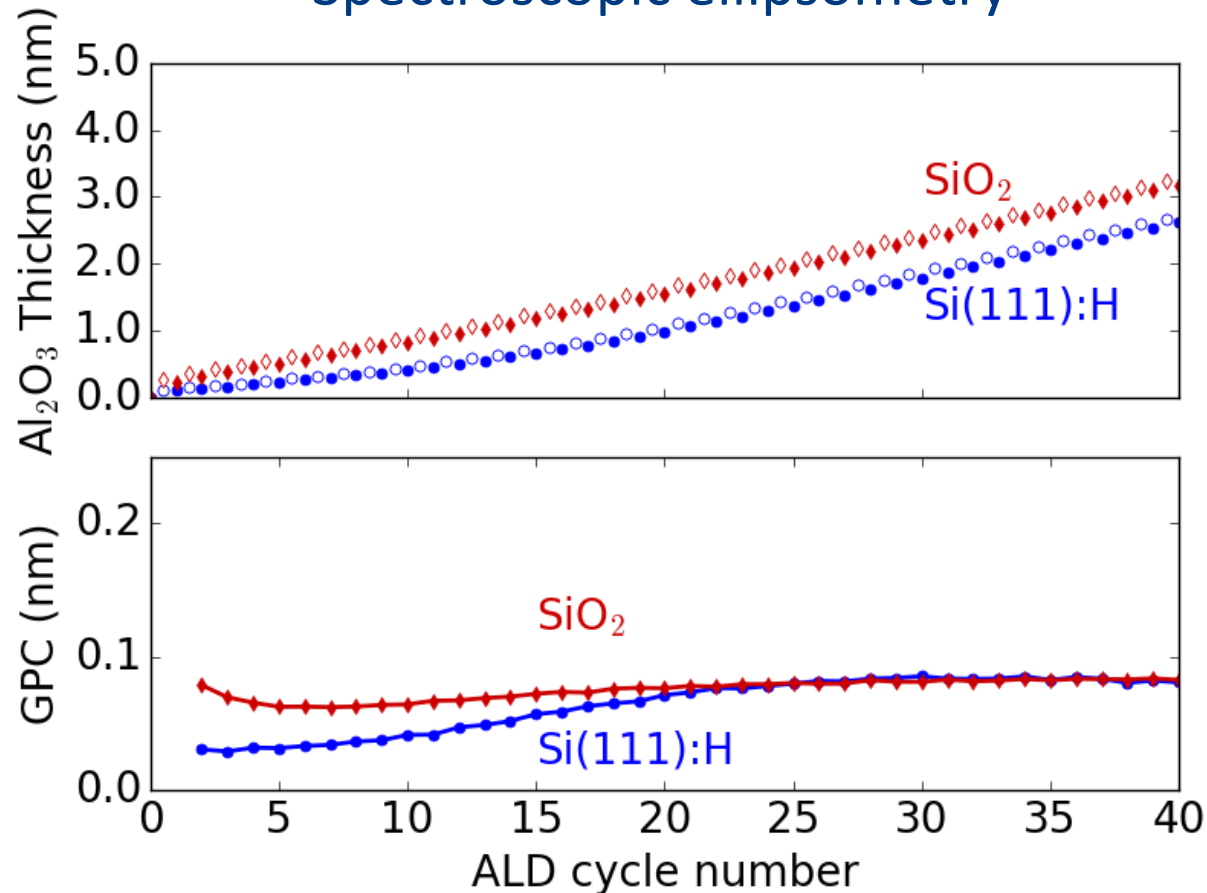
ALD Al_2O_3 on SiO_2 and $\text{Si}(111):\text{H}$ surfaces

Spectroscopic ellipsometry

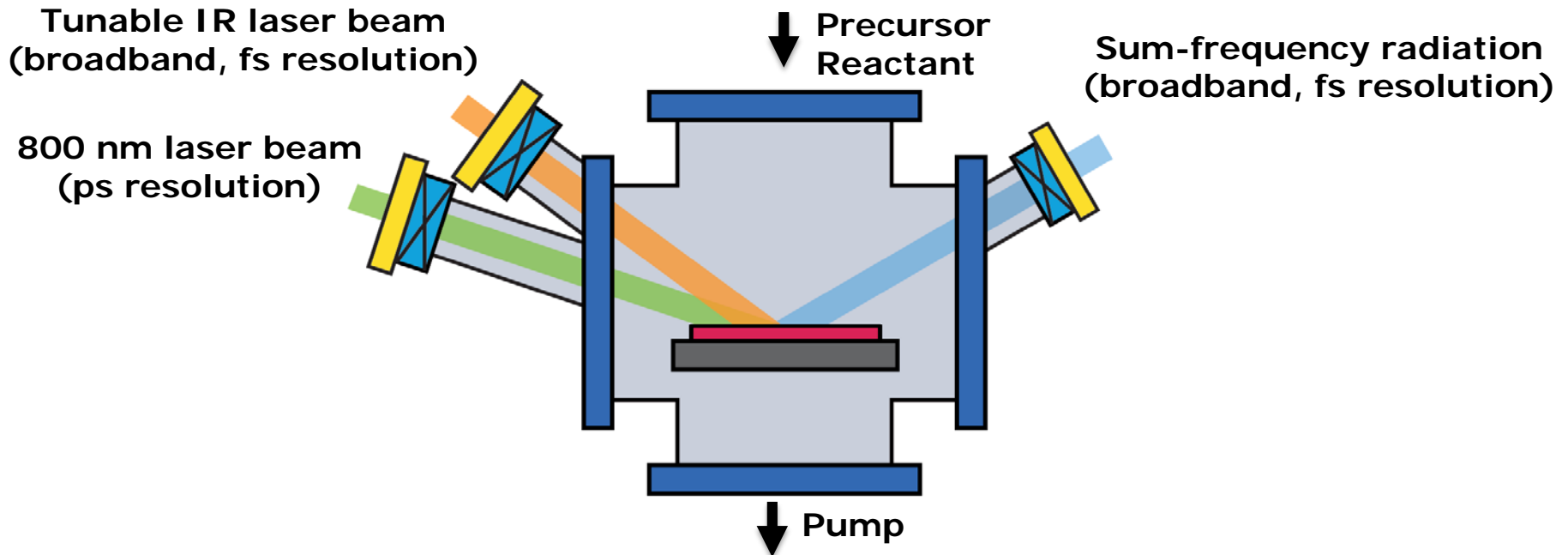
On foreign surfaces
initially **no “ideal”**
ALD film growth

Additional insight is
necessary for

- Ultrathin films
- Area-selective ALD
- Etc.



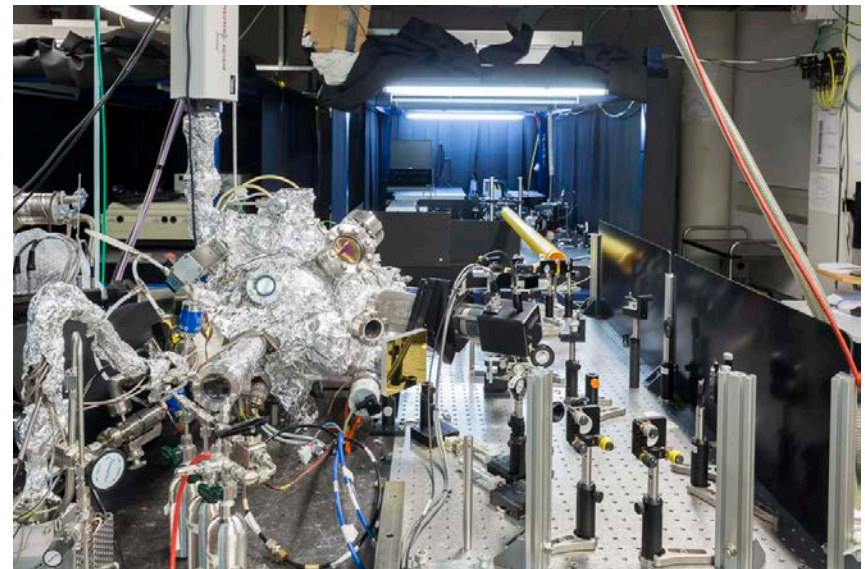
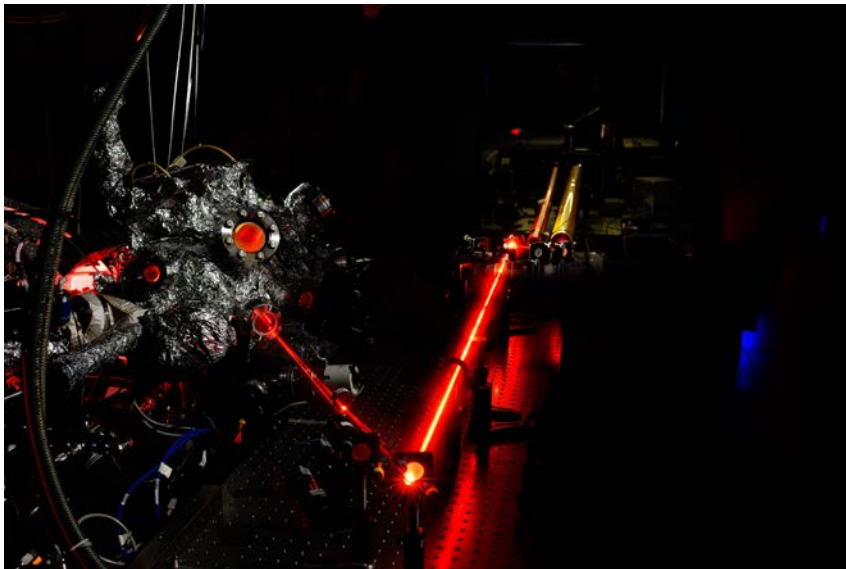
Sum frequency generation (SFG)



Nonlinear optical technique with 2 laser beams probing vibrational transitions

- ▲ • Highly sensitive & specific for surface groups (sub-surface species not probed)
- ▲ • Good time resolution, reaction kinetics can be followed in time
- ▲ • Can give absolute values of reaction cross-sections/sticking probabilities etc.
- ▼ • Very complex method requiring highly dedicated setup with laser-system

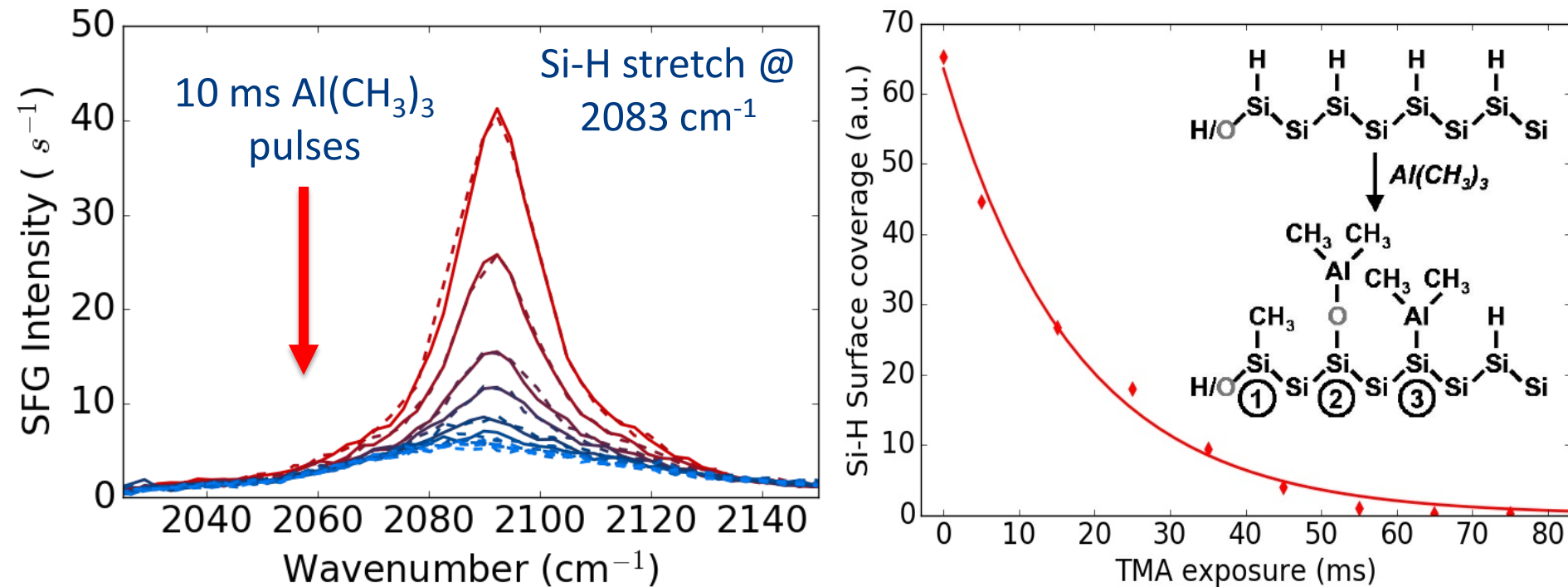
Sum frequency generation (SFG)



Nonlinear optical technique with 2 laser beams probing vibrational transitions

- ▲ • Highly sensitive & specific for surface groups (sub-surface species not probed)
- ▲ • Good time resolution, reaction kinetics can be followed in time
- ▲ • Can give absolute values of reaction cross-sections/sticking probabilities etc.
- ▼ • Very complex method requiring highly dedicated setup with laser-system

Sum frequency generation – Al_2O_3 on $\text{Si}(111):\text{H}$



$\text{Al}(\text{CH}_3)_3$ reacts with $\text{Si}(111):\text{H}$ breaking the Si-H bonds

Reaction cross-section $\sigma = (3.1 \pm 0.3) \times 10^{-18} \text{ cm}^2$

or translated into sticking probability $s_0 = (1.9 \pm 0.2) \times 10^{-3}$

Initial growth of Al_2O_3 on SiO_2 and on $\text{Si}(111):\text{H}$

Initial growth:

1st cycle on $\text{Si}(111):\text{H}$

$$s_0 = (1.9 \pm 0.2) \times 10^{-3}$$

1st cycle on SiO_2

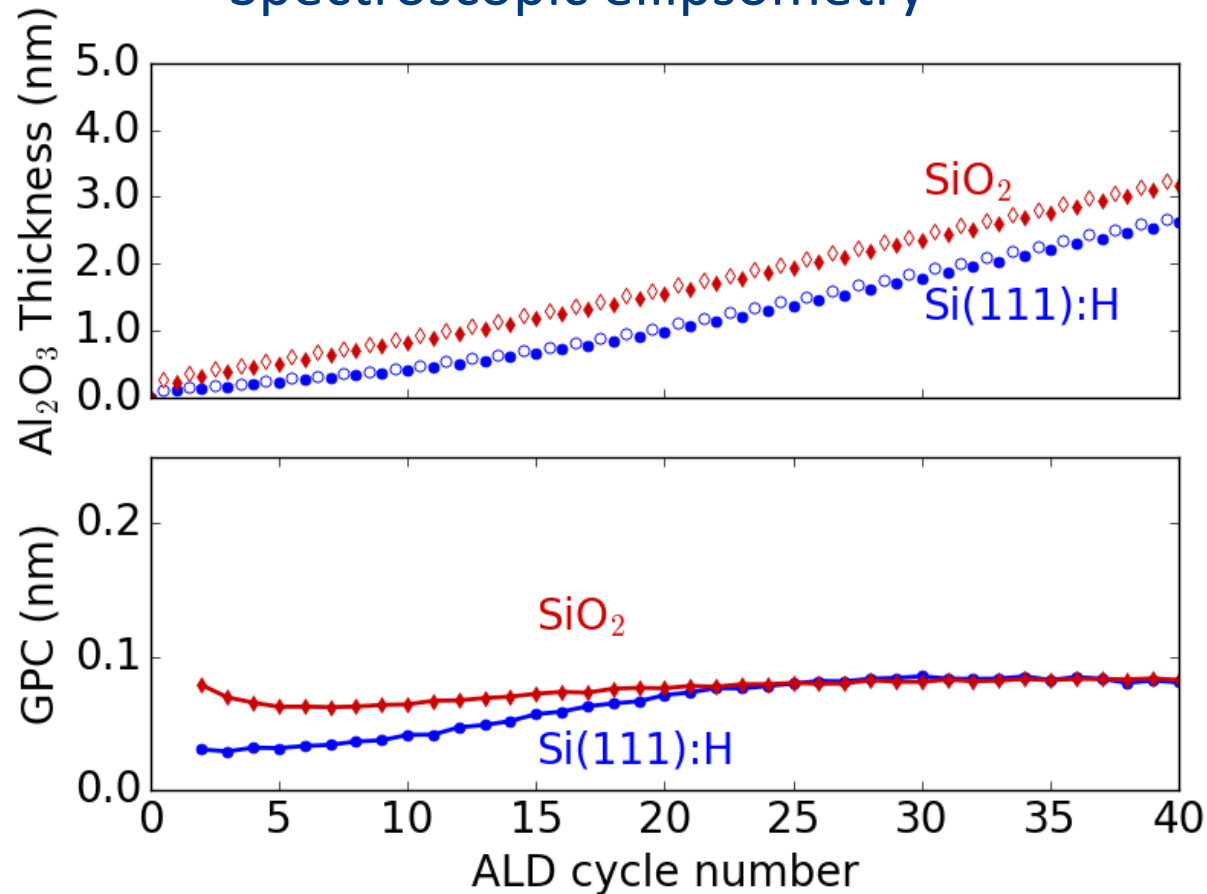
$$s_0 = (1.2 \pm 0.1) \times 10^{-3}$$

Steady-state growth:

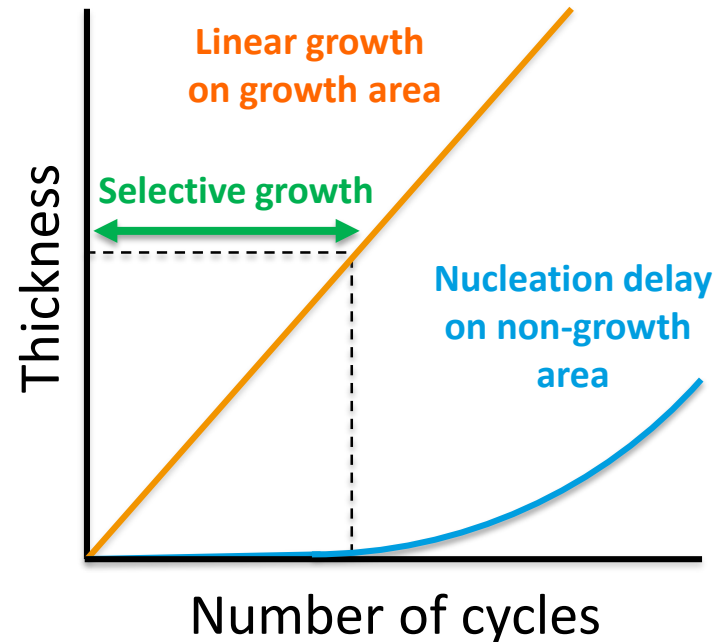
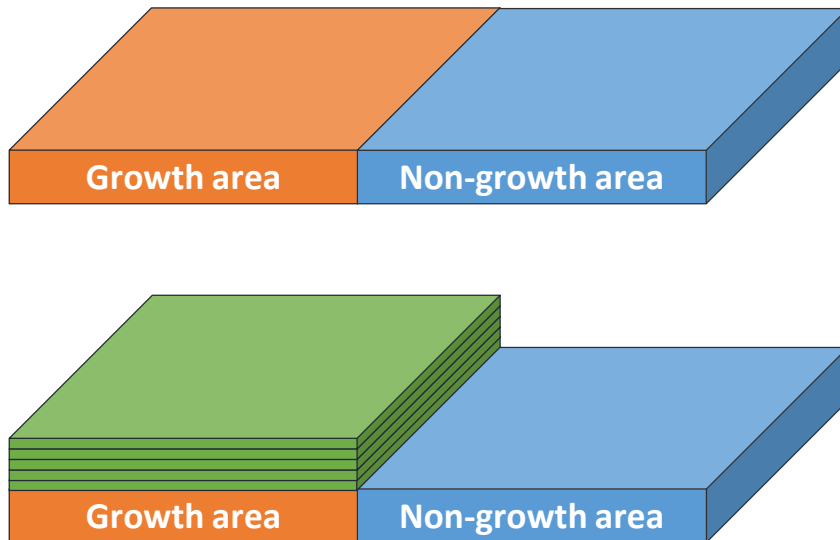
x-th cycle ($x \gg 1$)

$$s_0 = (3.9 \pm 0.4) \times 10^{-3}$$

Spectroscopic ellipsometry



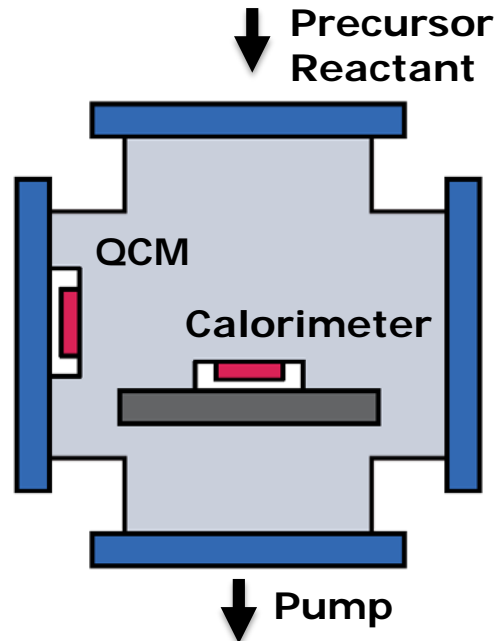
Area-selective ALD (see tutorial Parsons)



Differences in nucleation behavior (initial growth) are often exploited to achieve area-selective ALD

**Fundamental insight (preferable with quantitative information)
in initial growth is required**

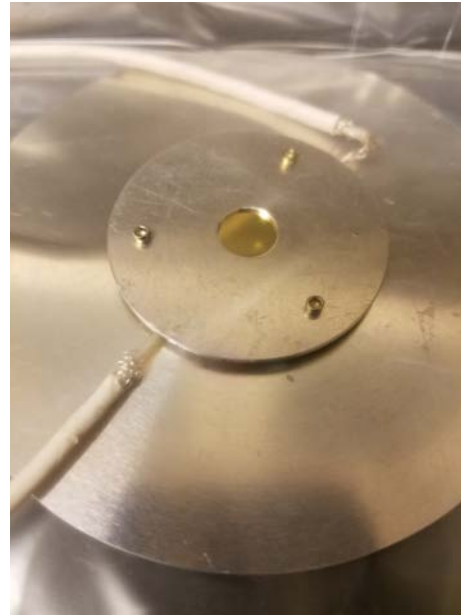
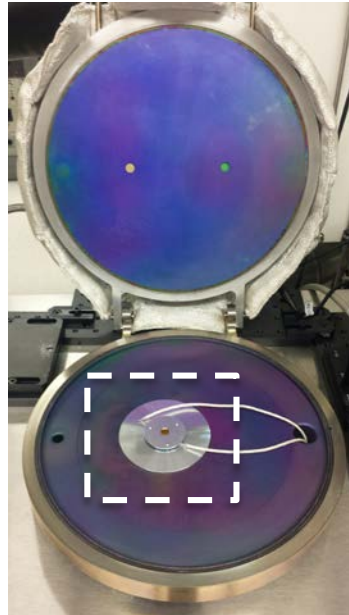
Adsorption calorimetry



Measures half-cycle reaction heats pyroelectrically using a LiTaO_3 crystal disk

- ▲ . Provides additional thermodynamic and mechanistic insight
- ▲ . Can be used to verify and benchmark (half-cycle) reactions – also from DFT
- ▼ . New to the field of ALD – needs follow up work
- ▼

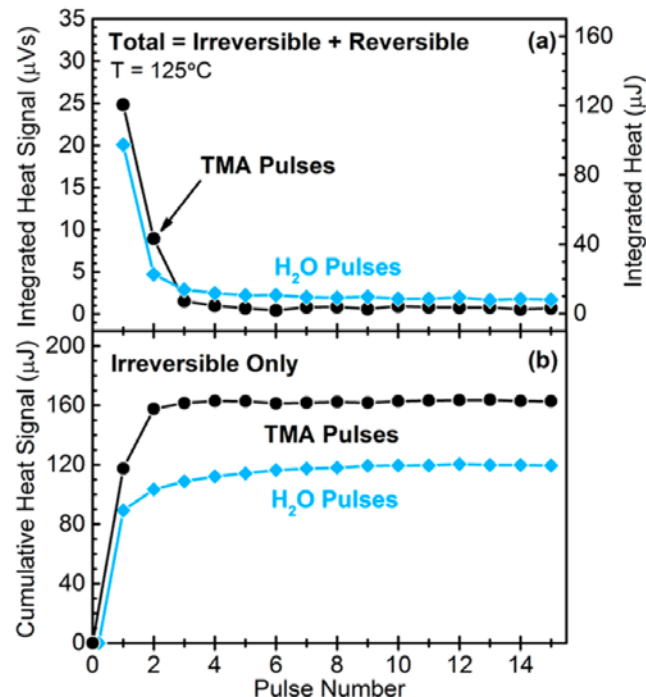
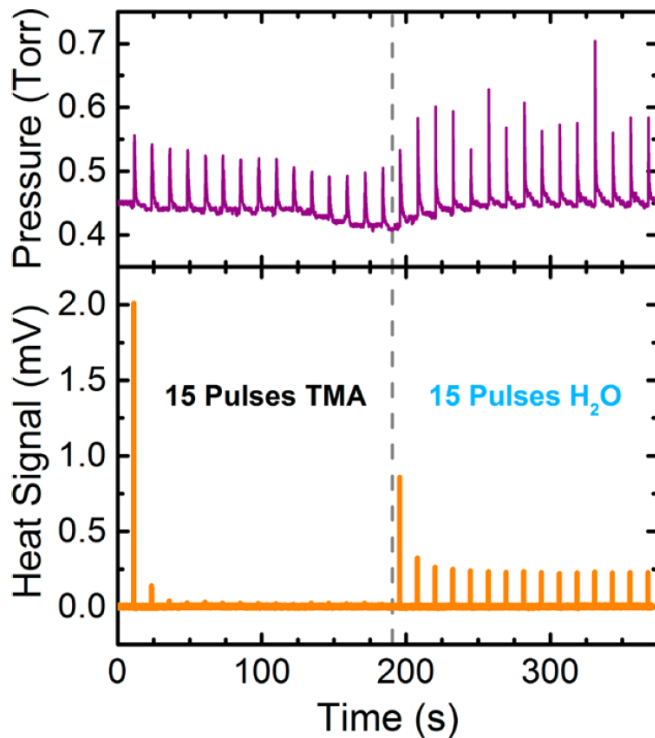
Adsorption calorimetry



Measures half-cycle reaction heats pyroelectrically using a LiTaO_3 crystal disk

- ▲ . Provides additional thermodynamic and mechanistic insight
- ▲ . Can be used to verify and benchmark (half-cycle) reactions – also from DFT
- ▼ . New to the field of ALD – needs follow up work
- ▼

Adsorption calorimetry – Reaction heats (Al_2O_3)



A - 1st Half Cycle:

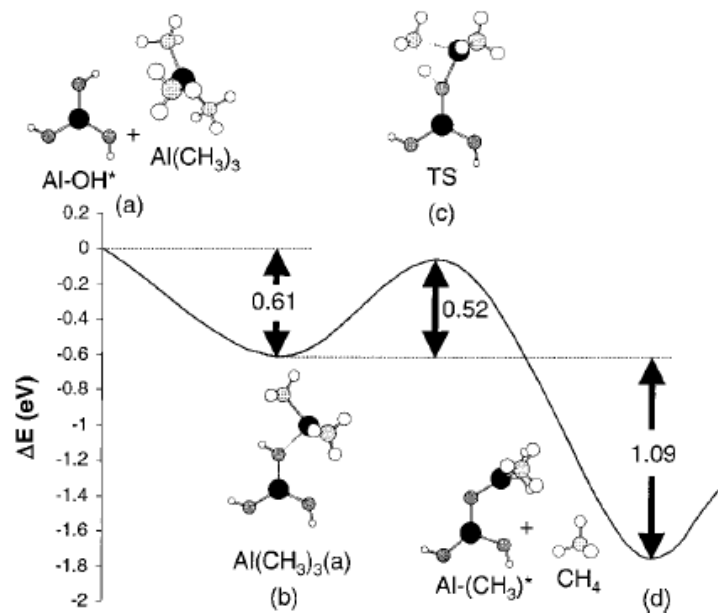


B - 2nd Half Cycle:

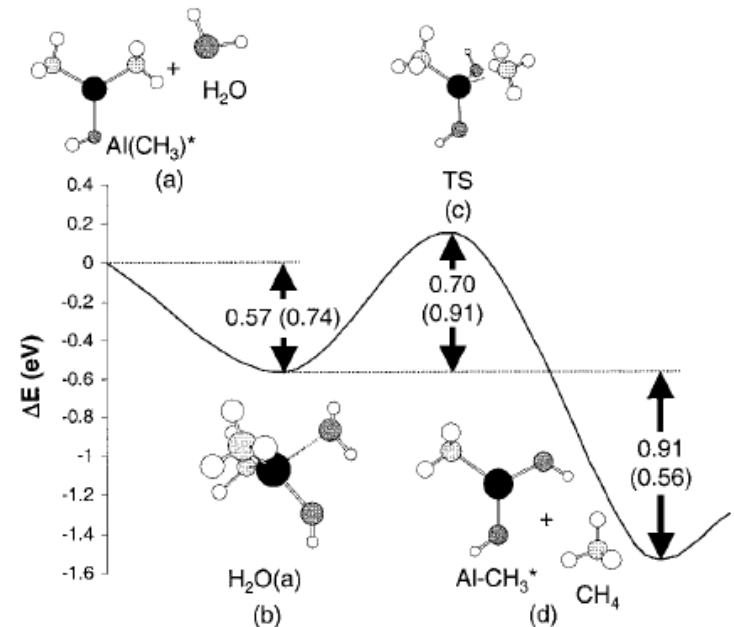


First-principle calculations

A - 1st Half Cycle



B - 2nd Half Cycle

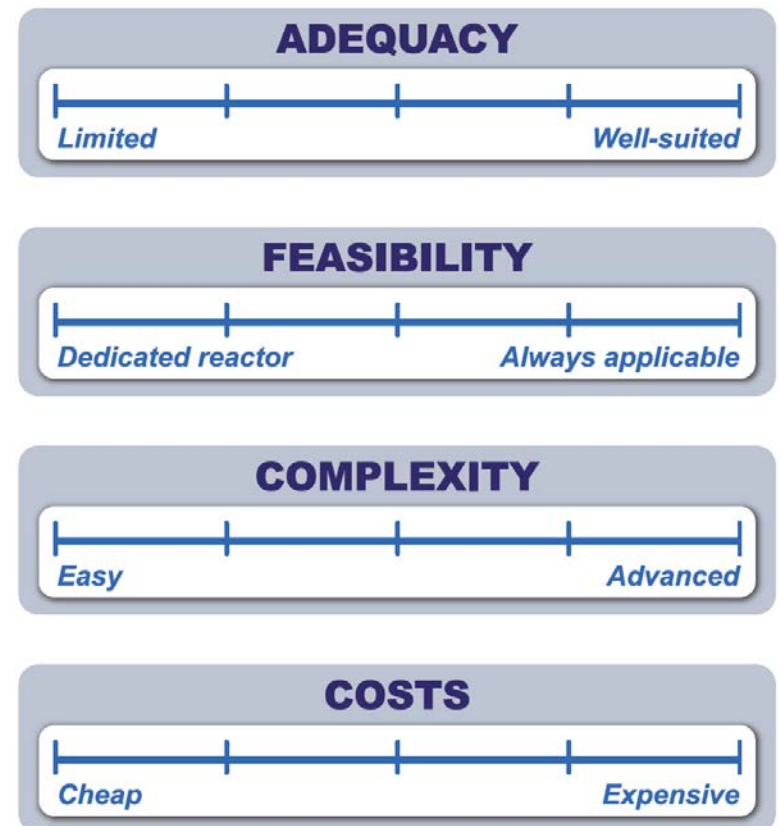


So far calculated reaction heats have remained
untested with respect to experiment

Concluding remarks

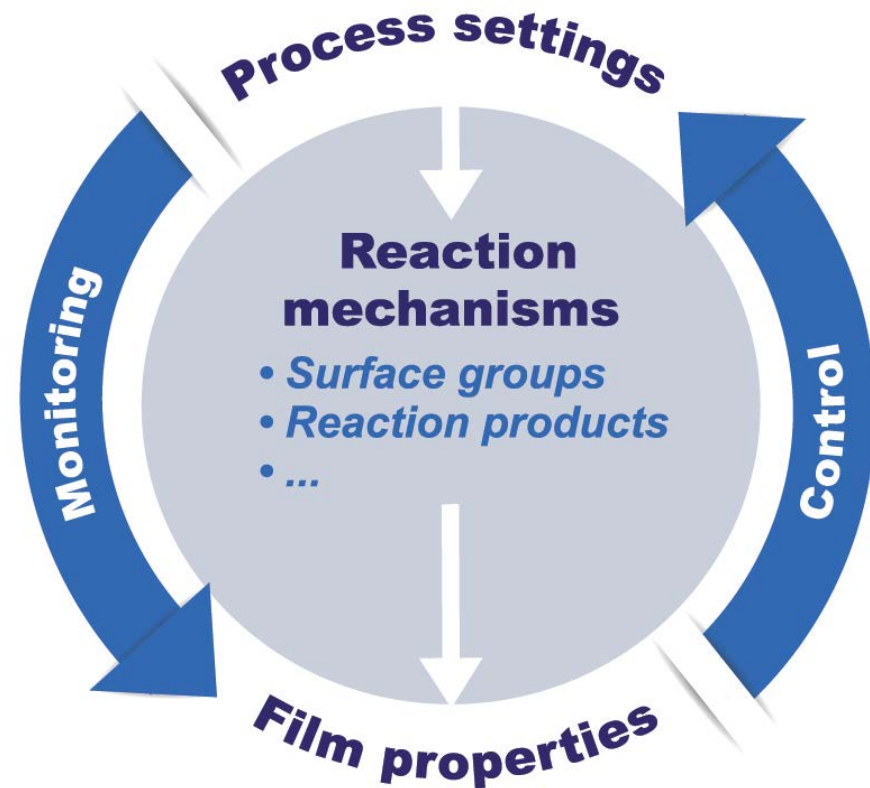
- Various analytical tools for *in situ* studies of ALD have been discussed
QMS, gas phase FTIR, QCM, SE, surface FTIR, OES

Many more exist. Combine tools if you can!



Concluding remarks

- Various analytical tools for *in situ* studies of ALD have been discussed
QMS, gas phase FTIR, QCM, SE, surface FTIR, OES
Many more exist. Combine tools if you can!
- Focus can be on
 - Film growth & properties
 - Reaction mechanisms
 - Process monitoring & control



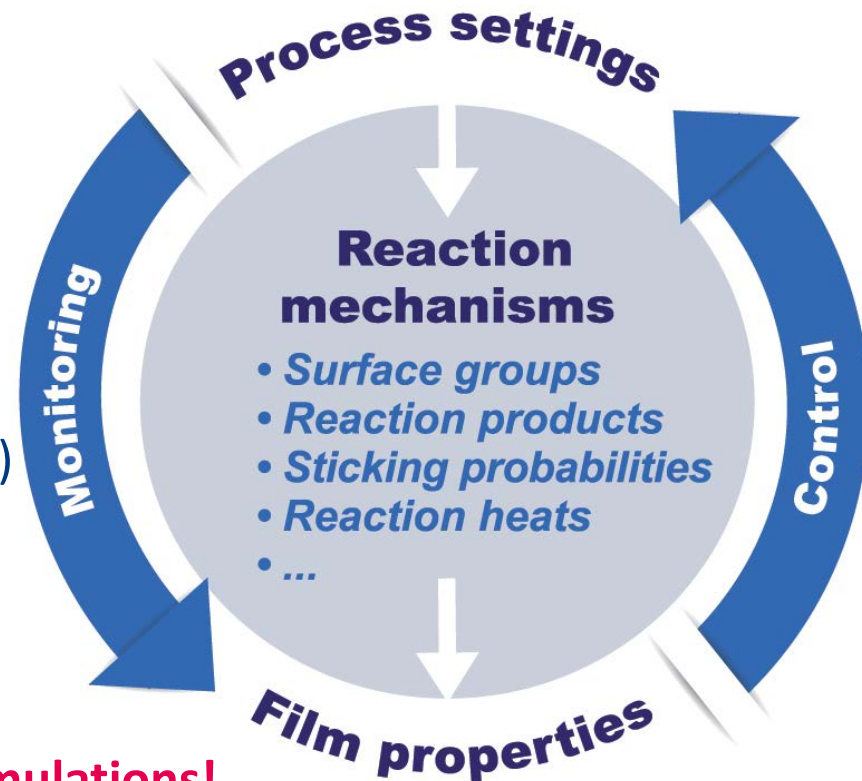
Concluding remarks

- Various analytical tools for *in situ* studies of ALD have been discussed
QMS, gas phase FTIR, QCM, SE, surface FTIR, OES

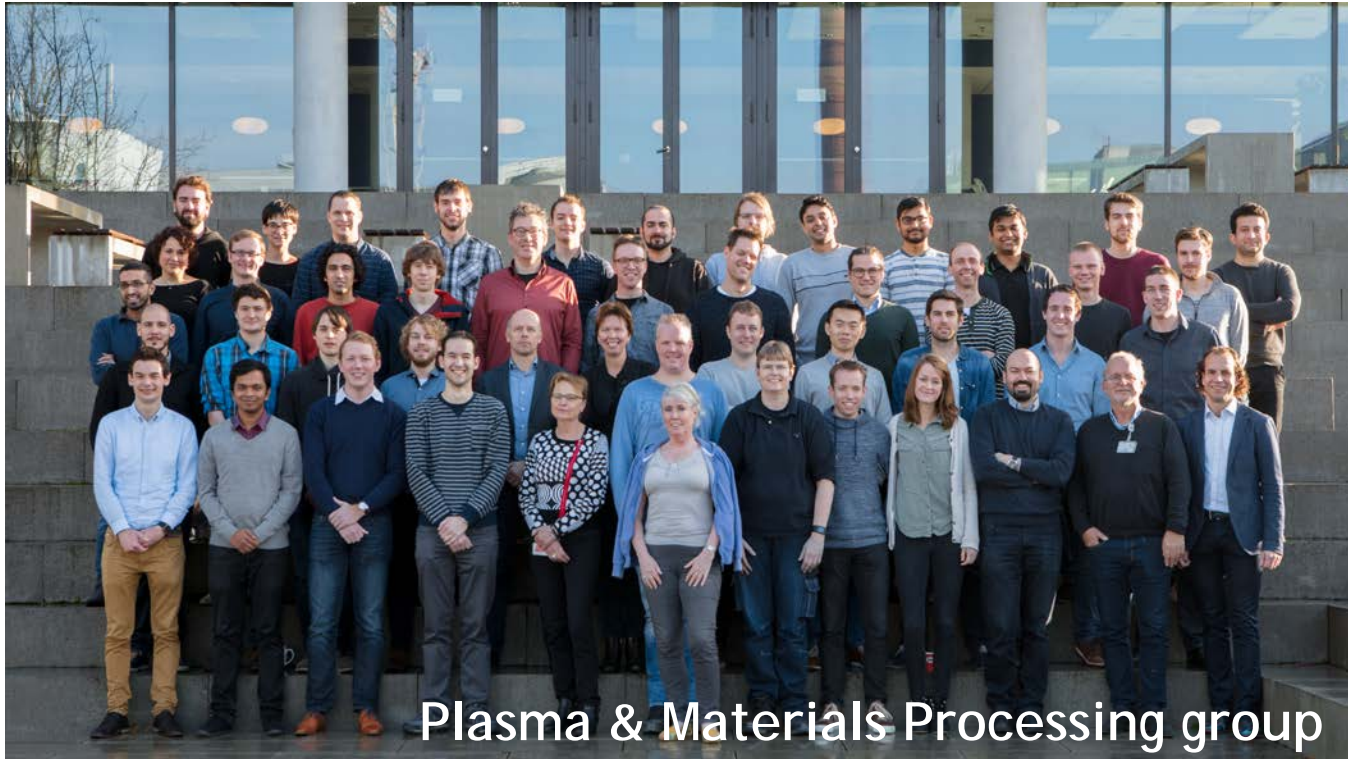
Many more exist. Combine tools if you can!

- Focus can be on
 - Film growth & properties
 - Reaction mechanisms
 - Process monitoring & control
- Take it to the next level (**quantitatively!**)
 - Sticking probabilities
 - Reaction heats
 - Transient states
 -

Combine experiments with theory/simulations!



Acknowledgements



Co-workers:

Dr. Adrie Mackus
Dr. Harm Knoops
Dr. Fred Roozeboom
Dr. Marcel Verheijen
Dr. Ageeth Bol
Dr. Adriana Creatore
&
Many PhD students
and postdocs



For more information & feedback
see blog:

www.AtomicLimits.com



Mission: educate students and professionals on the principles, applications and future advancements of ALD and related atomic-scale processes.



Dr. Gregory Parsons
*Dept. of Chemical and Biomolecular Engineering
North Carolina State University*



Dr. Erwin Kessels
*Dept. of Applied Physics
Eindhoven University of Technology*